



Analog to Digital in a Few Simple Steps

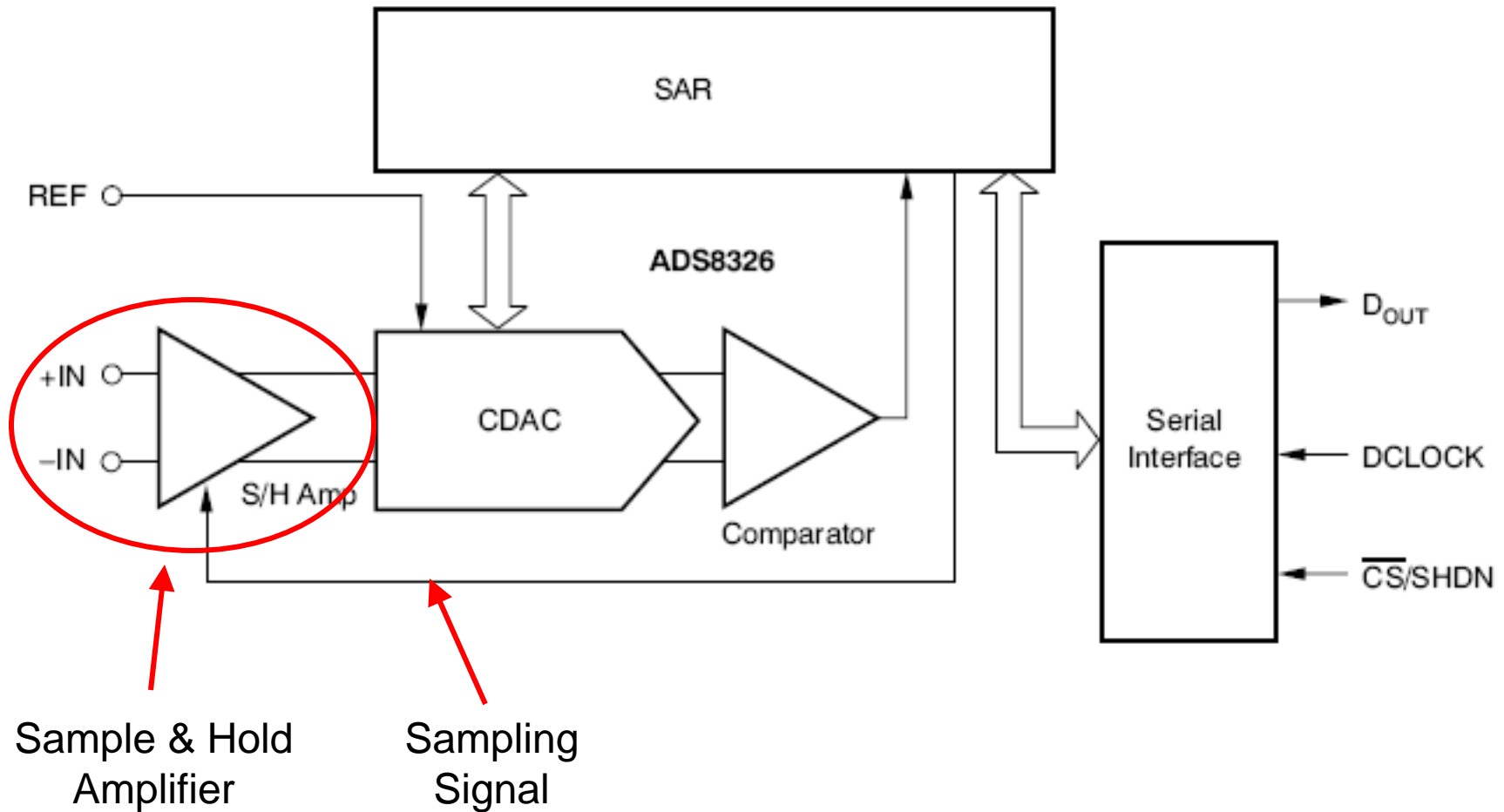
A Guide to Designing with SAR ADCs



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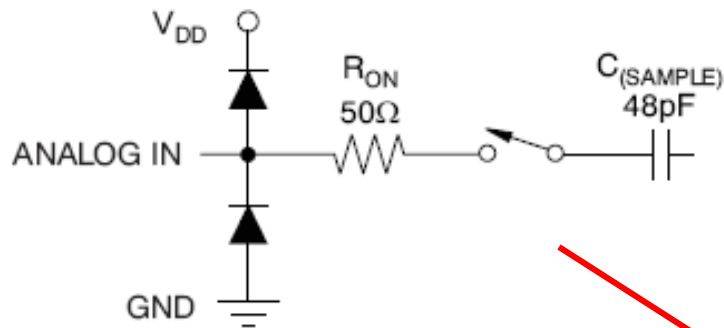


SAR ADC's Block Diagram



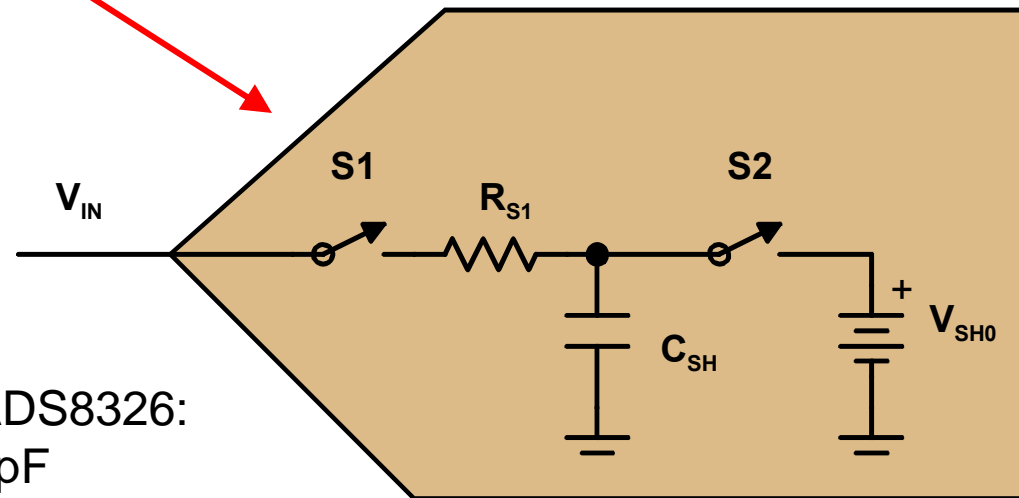


Equivalent Input Circuit



Diode Turn-On Voltage: 0.35V
Equivalent Analog Input Circuit

SAR ADC Sample & Hold Amplifier



- From the Data Sheet for ADS8326:
- Sampling capacitor is 48pF
 - Sampling switch resistance is 50 Ω

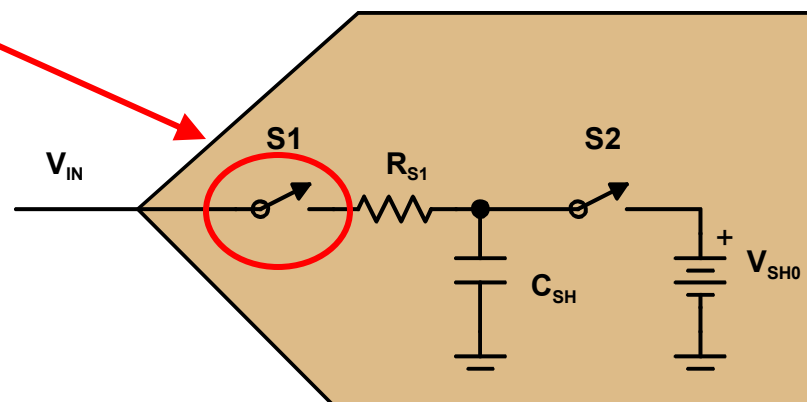
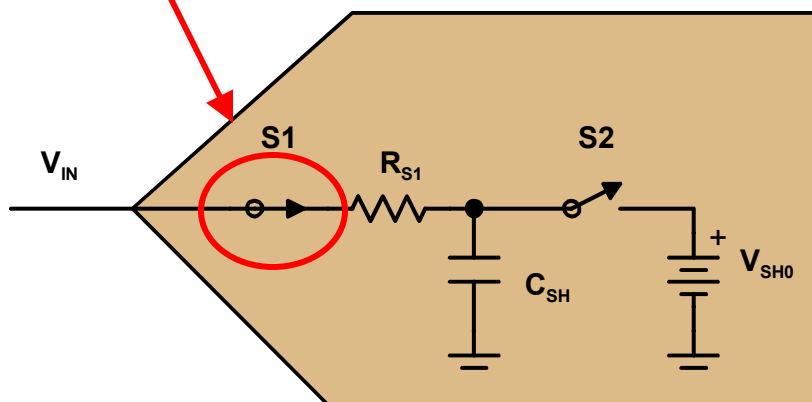


Sample and Conversion Process

ELECTRICAL CHARACTERISTICS: $V_{DD} = +5V$

At $-40^{\circ}C$ to $+85^{\circ}C$, $V_{REF} = +5V$, $-IN = GND$, $f_{SAMPLE} = 250kHz$, and $f_{DCLOCK} = 24 \times f_{SAMPLE}$, unless otherwise noted.

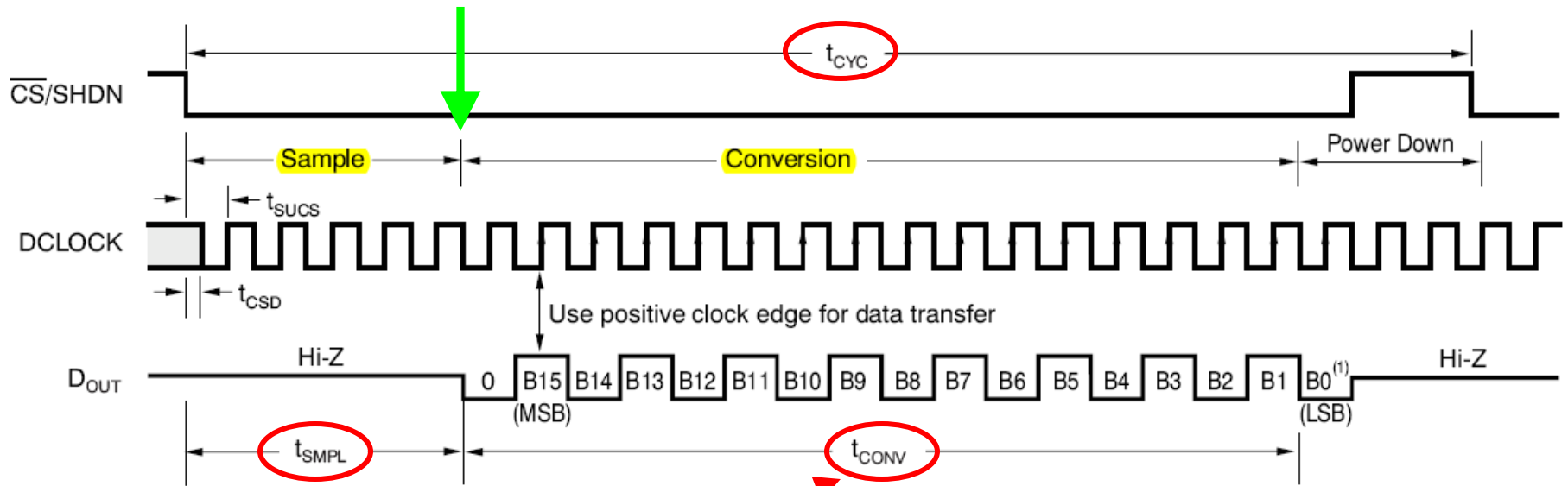
PARAMETER	TEST CONDITIONS	ADS8326I			ADS8326IB			UNIT
		MIN	TYP	MAX	MIN	TYP	MAX	
SAMPLING DYNAMICS								
Conversion time (16 DCLOCKS)	t_{CONV}	$24kHz \leq f_{DCLOCK} \leq 6MHz$	2.667		666.7	2.667	666.7	μs
Acquisition time (4.5 DCLOCKS)	t_{AQ}	$f_{DCLOCK} = 6MHz$	0.75			0.75		μs
Throughput rate (22 DCLOCKS)				250			250	kSPS
Clock frequency	f_{DCLOCK}		0.024	6		0.024	6	MHz





Sample and Conversion Timing

TIMING INFORMATION



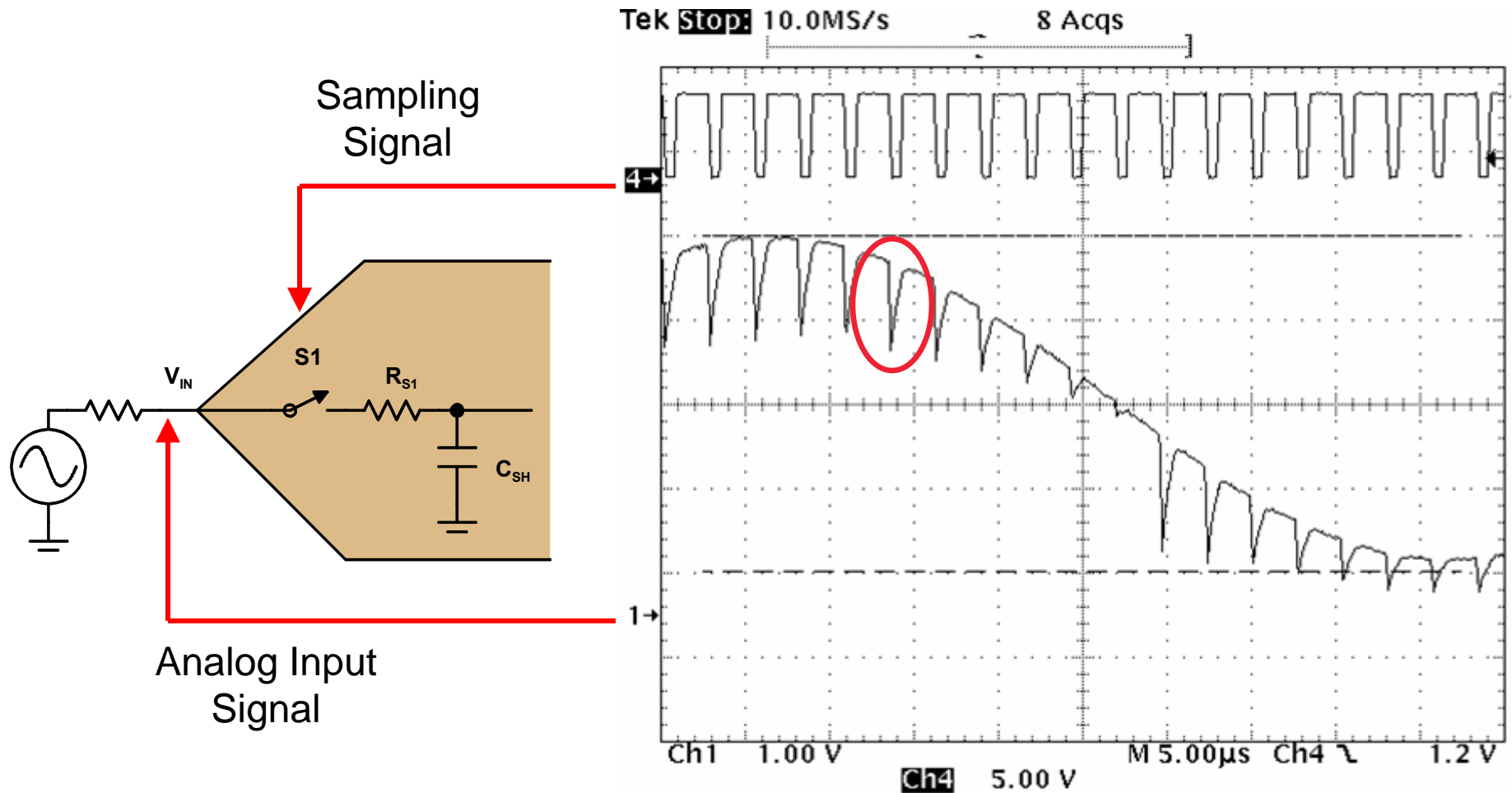
NOTE: (1) A minimum of 22 clock cycles are required for 16-bit conversion; 24 clock cycles are shown.

Table 1. Timing Characteristics

SYMBOL	DESCRIPTION	MIN	TYP	MAX	UNIT
t_{SMPL}	Analog input sample time	4.5		5.0	DCLOCKs
t_{CONV}	Conversion time		16		DCLOCKs
t_{CYC}	Complete cycle time	22			DCLOCKs

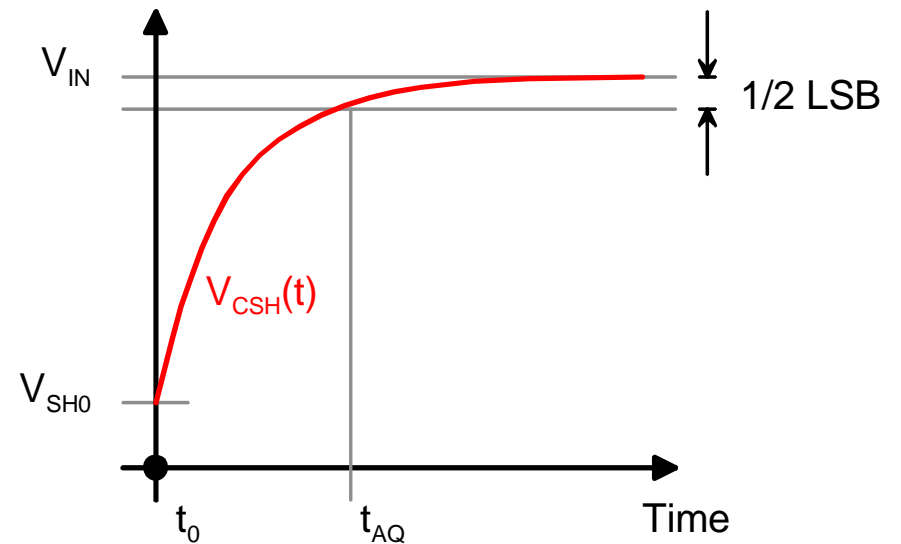
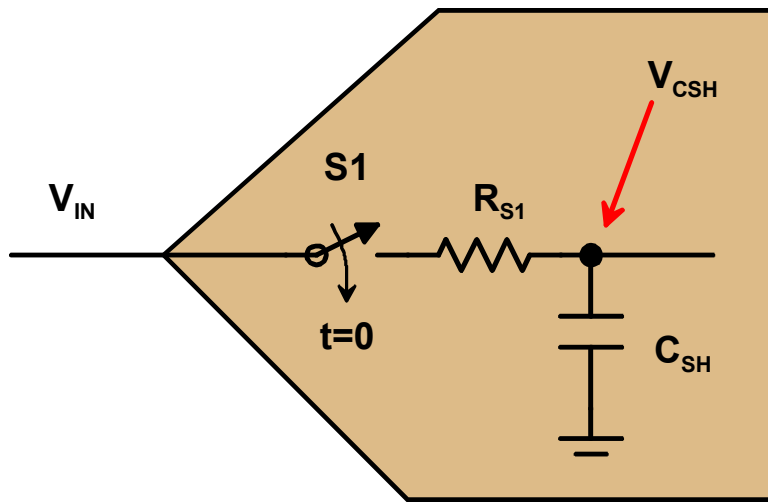


Voltage Ripple on The Input of ADC





Voltage Across Sampling Capacitor



$$V_{CSH}(t) = V_{CSH}(t_0) + [V_{IN} - V_{CSH}(t_0)] \times (1 - e^{-\frac{t}{\tau}})$$

$$\tau = R_{S1} \times C_{SH}$$



Settling Time as a Function of Time Constant

$$V_{IN} - V_{CSH}(t_{AQ}) \leq \frac{1}{2} LSB$$

$V_{CSH}(t_{AQ})$ is voltage across the C_{SH} , at the end of the sampling period

t_{AQ} is acquisition time, the time from the beginning of the sampling period (t_0) to the end of the sampling period

$$\frac{1}{2} LSB = \frac{FSR}{2^{N+1}}$$

(LSB = Least Significant Bit, FSR is the full-scale range of the N-Bit converter)

$$t_{AQ} \geq k_1 \times \tau$$

$$k_1 = (N + 1) \times \ln(2)$$



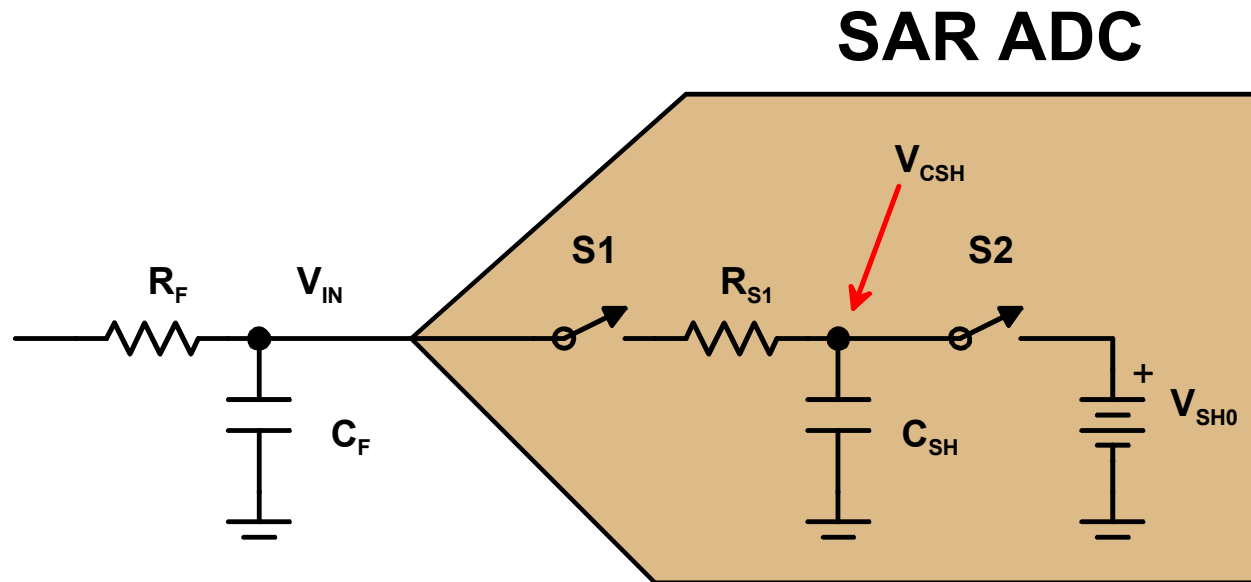
Time-Constant-Multiplier (k_1) for SAR ADC

ADC Resolution	k_1 time-constant-multiplier 1/2 LSB accuracy, $1/2^{N+1}$
8	6.2
10	7.6
12	<u>9.0</u>
14	10.4
16	<u>11.8</u>
18	13.2
20	14.6

*note – using worst case values: $V_{IN} = \text{full-scale voltage or } 2^N$, $V_{SH0} = 0V$



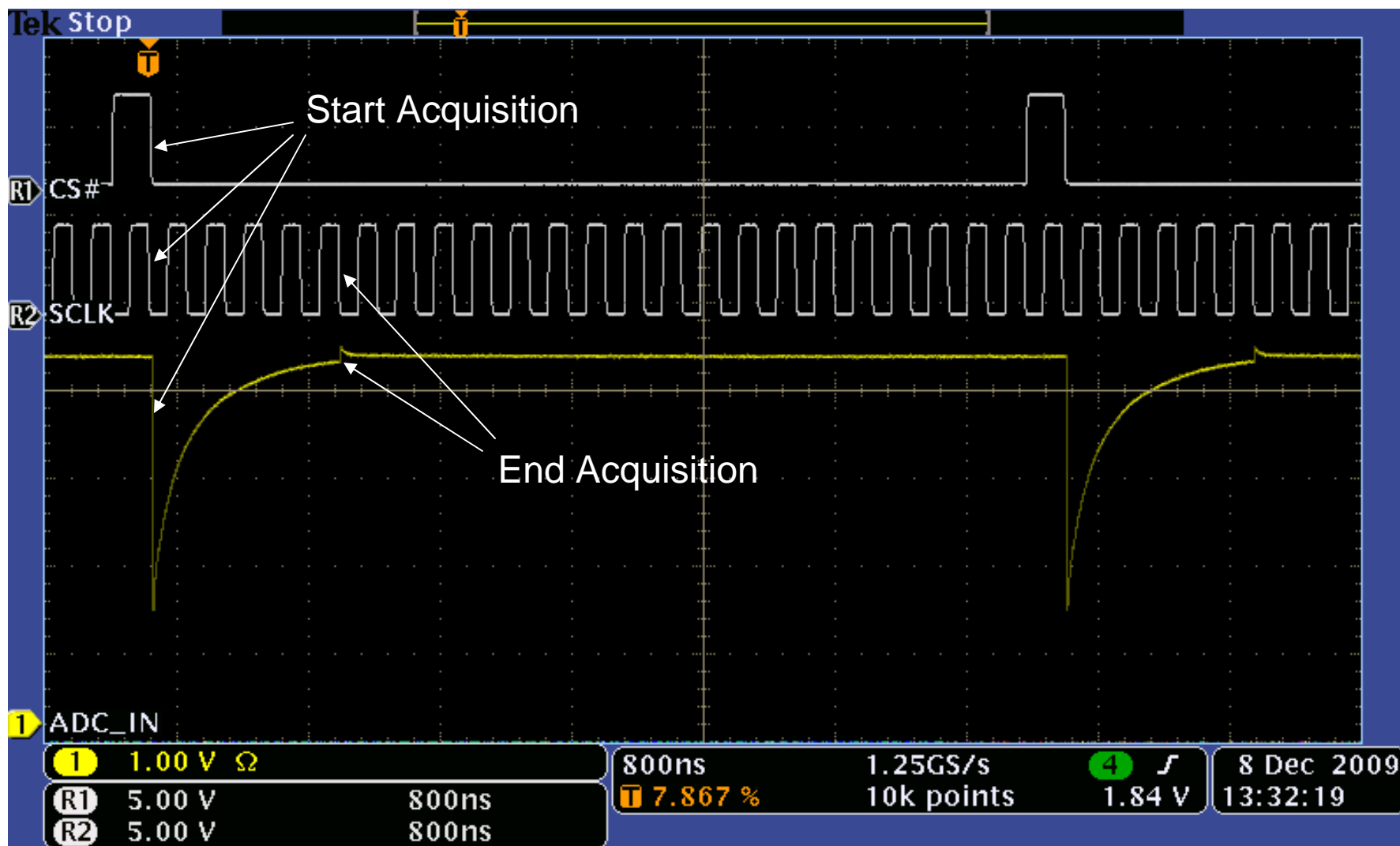
SAR ADC With Input RC Filter



$$R_F \times C_F \leq \frac{t_{AQ}}{(N + 1) \cdot \ln(2)}$$

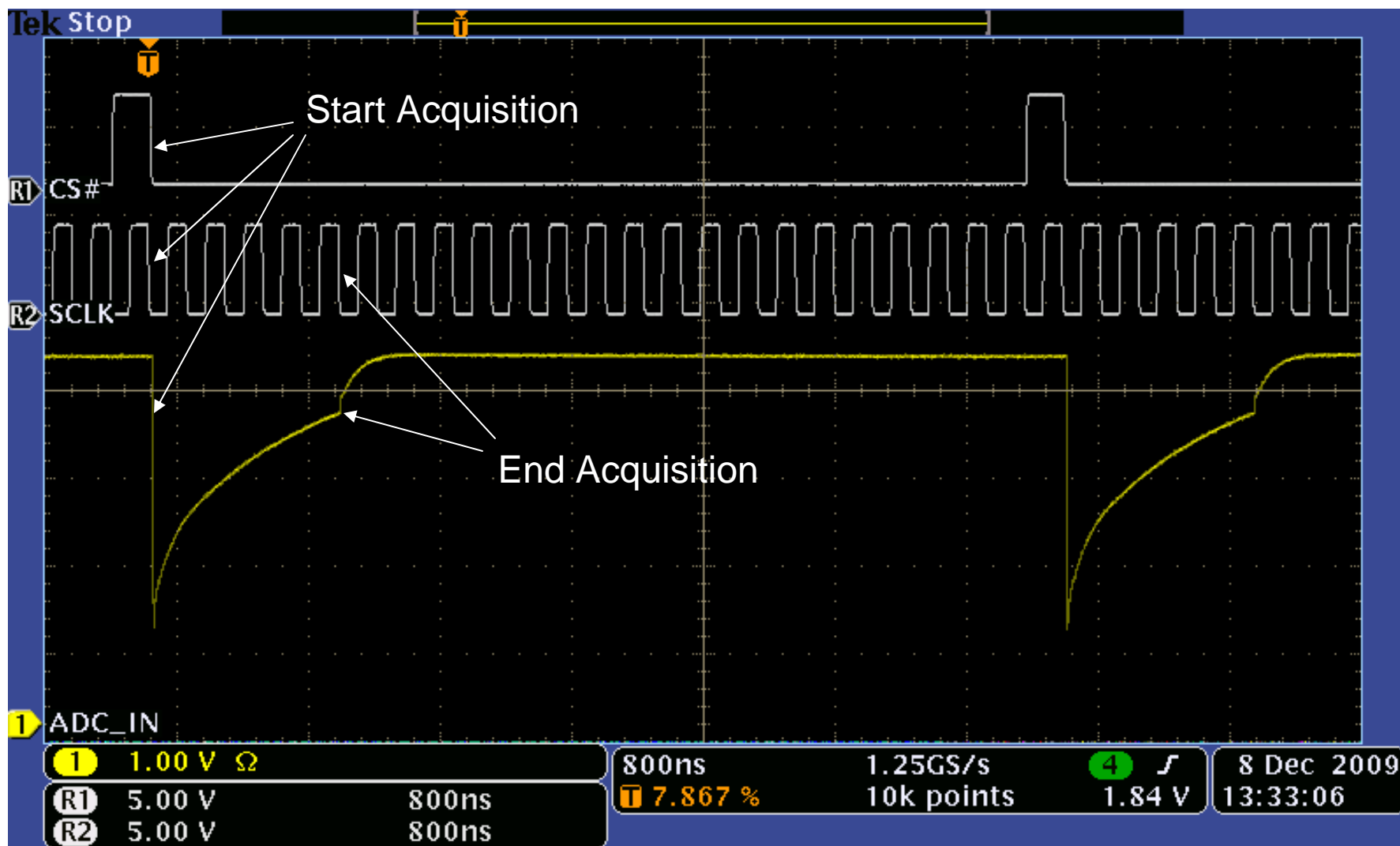


ADC Input With Proper RC Filter



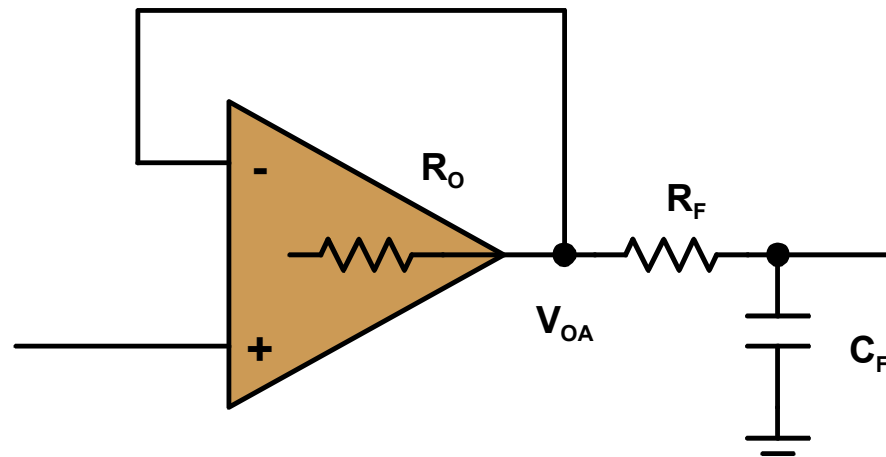


ADC Input With Wrong RC Filter



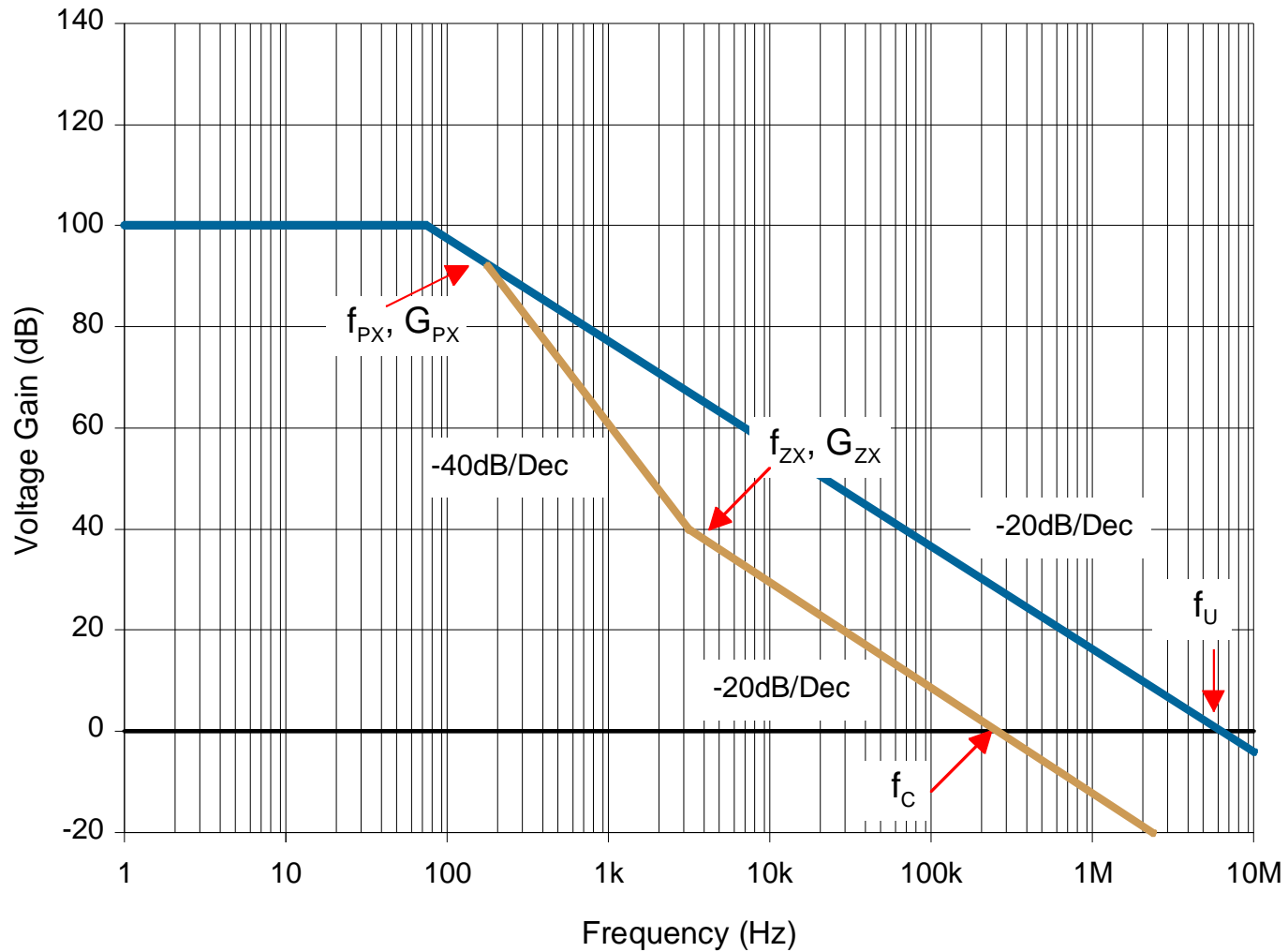


Op Amp Driving RC Filter





Modified Open-Loop Voltage Gain





Added Pole and Zero

Frequency of added pole

$$f_{PX} = \frac{1}{2\pi \cdot (R_O + R_F) \cdot C_F}$$

Frequency of added zero

$$f_{ZX} = \frac{1}{2\pi \cdot R_F \cdot C_F}$$

Gain of added pole

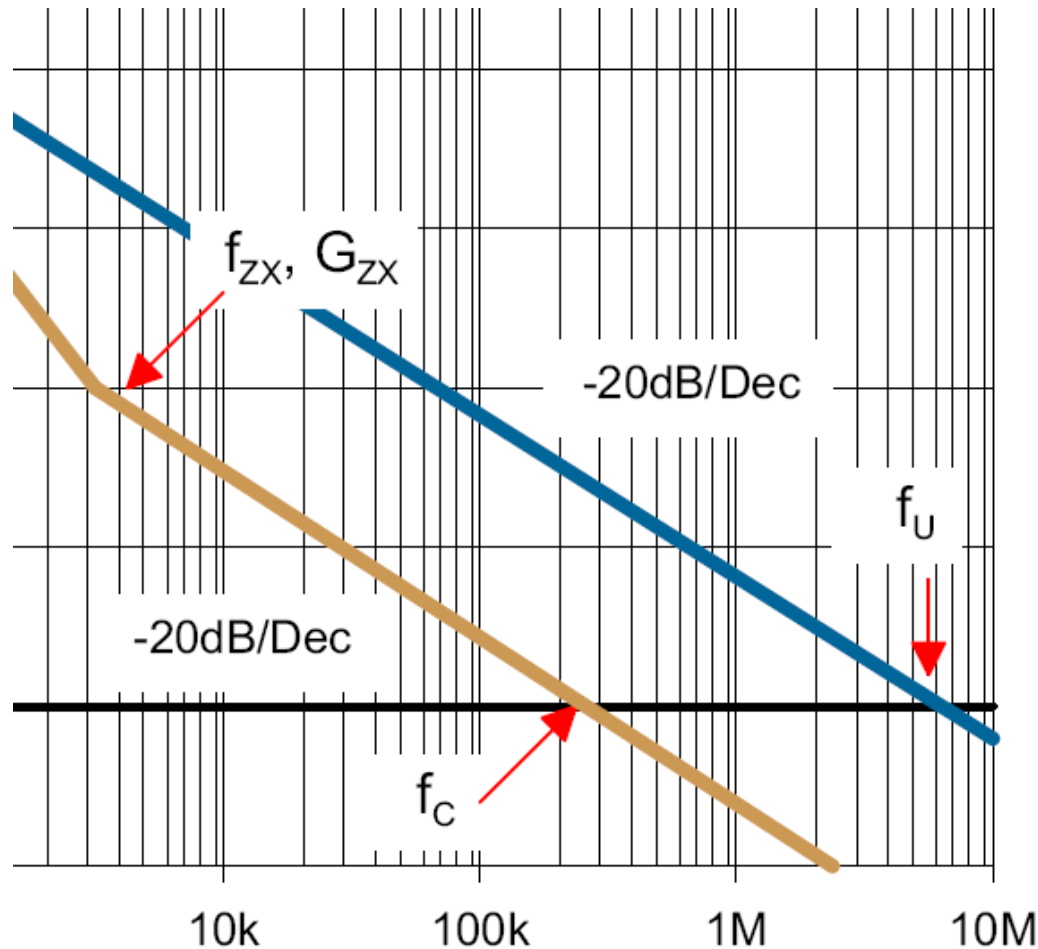
$$G_{PX} = -20 \cdot \log \left[\frac{f_{PX}}{f_U} \right]$$

Gain of added zero

$$G_{ZX} = G_{PX} - 40 \cdot \log \left[\frac{f_{ZX}}{f_{PX}} \right]$$



Good Design Guideline



$$f_C \leq \frac{1}{2} f_U$$

$$f_{ZX} \leq \frac{1}{2} f_C$$

or

$$f_{ZX} \leq \frac{1}{4} f_U$$

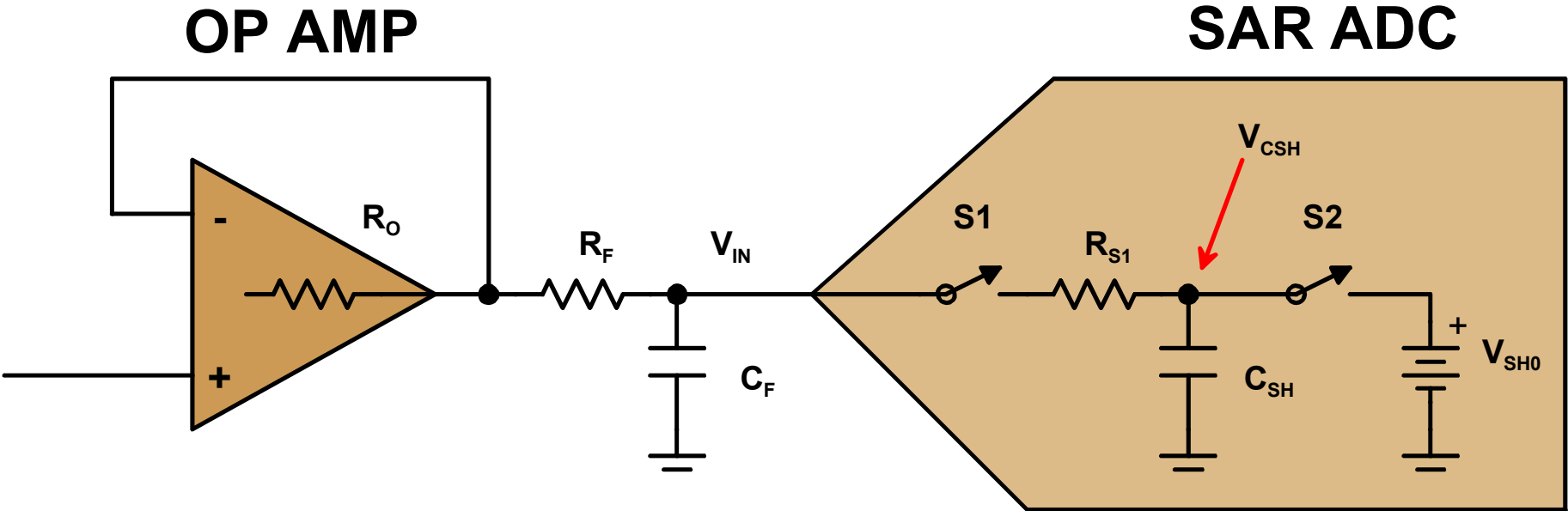
$$G_{ZX} \geq +6dB$$

$$f_{PX} > \frac{1}{10} f_{ZX}$$

$$R_F \geq \frac{R_O}{9}$$



Final Circuit





Minimum Acquisition Time and Op Amp's GBW

- Calculate time-constant multiplier

$$k = (N + 1) \cdot \ln(2)$$

- Determine minimum time-constant

$$\tau \leq \frac{t_{AQ}}{k}$$

- Calculate frequency of added zero

$$f_{ZX} = \frac{1}{2\pi \cdot \tau}$$

- Find Unity Gain Bandwidth

$$GBW = 4 \cdot f_{ZX}$$

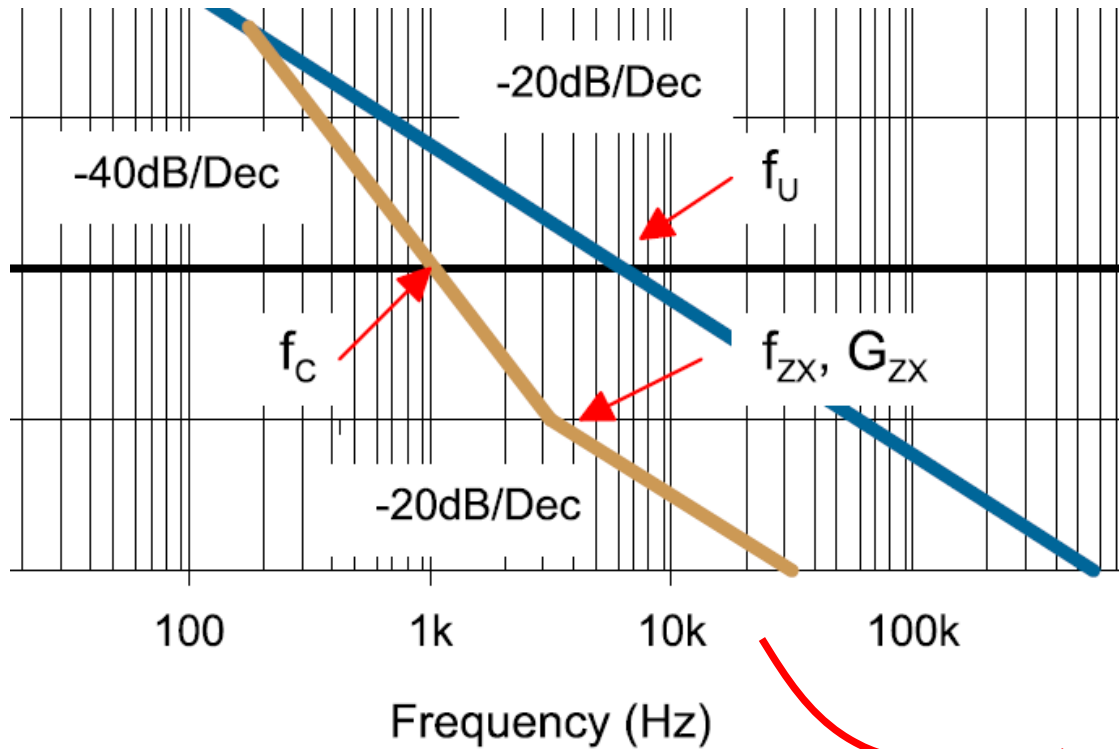


Minimum Acquisition Time for Different Op Amps

		GBW (MHz)	f_z (MHz)	τ (ns)	12 Bit t_{AQ} (ns)	16 Bit t_{AQ} (ns)
INA155	Medium Speed, Precision INA	0.55	0.14	1,157	5,672	8,881
INA128	High Precision, 120dB CMRR	1.3	0.33	490	2,400	3,757
INA331	High Bandwidth, Single Supply	5.0	1.25	127	624	977
OPA340	CMOS, 0.0007% THD+N	5.5	1.38	116	567	888
OPA363	1.8V, High CMRR, SHDN	7.0	1.75	91	446	698
OPA2613	Dual VFB, Low Noise	12.5	3.13	51	250	391
OPA627	Ultra-Low THD+N, Wide BW	16.0	4.00	40	195	305
OPA381	Precision High-Speed Amp	18.0	4.50	35	173	271
OPA727	CMOS, e-trim™, Low Noise	20.0	5.00	32	156	244
OPA228	Precision, Low Noise, $G \geq 5$	33.0	8.25	19	95	148
OPA350	Precision ADC Driver	38.0	9.50	17	82	129
OPAy365	High-Speed, Zero-Crossover	50.0	12.50	13	62	98
OPA2889	Dual, Low Power, VFB	75.0	18.75	8	42	65
OPA211	36V, Bipolar Precision	80.0	20.00	8	39	61
THS4281	Very Low Power RRIO	80.0	20.00	8	39	61
OPA358	CMOS, 3V Operation, SC70	80.0	20.00	8	39	61



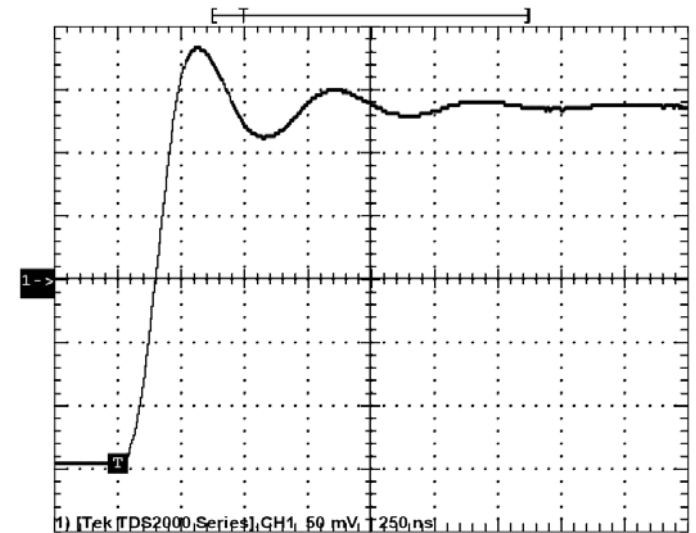
Not Good Design Guideline



$$f_C \leq f_{ZX}$$

or

$$G_{ZX} \leq 0dB$$



Stability Problem



After selecting ADC and OpAmp

- Determine C_F
- Calculate R_F
- Verify value R_F
- Calculate frequency of added pole
- Keep added pole and zero less than a decade apart

$$20 \cdot C_{SH} \leq C_F \leq 60 \cdot C_{SH}$$



$$R_F = \frac{1}{2\pi \cdot C_F \cdot f_{ZX}}$$

$$R_F \geq \frac{R_O}{9}$$

$$f_{PX} = \frac{1}{2\pi \cdot (R_F + R_O) \cdot C_F}$$

$$f_{PX} \geq \frac{1}{10} f_{ZX}$$



Design by Example

For ADS8326 we have $t_{AQ}=750ns$, $C_{SH}=48pF$ and $N=16$.

1
$$\left[\begin{aligned} k &= (N + 1) \cdot \ln(2) = (16 + 1) \cdot \ln(2) = 11.78 \\ \tau &\leq \frac{t_{AQ}}{k} = \frac{750ns}{11.78} = 63.65ns \\ f_{ZX} &= \frac{1}{2\pi \cdot \tau} = \frac{1}{2\pi \cdot 63.65ns} = 2.5MHz \end{aligned} \right.$$

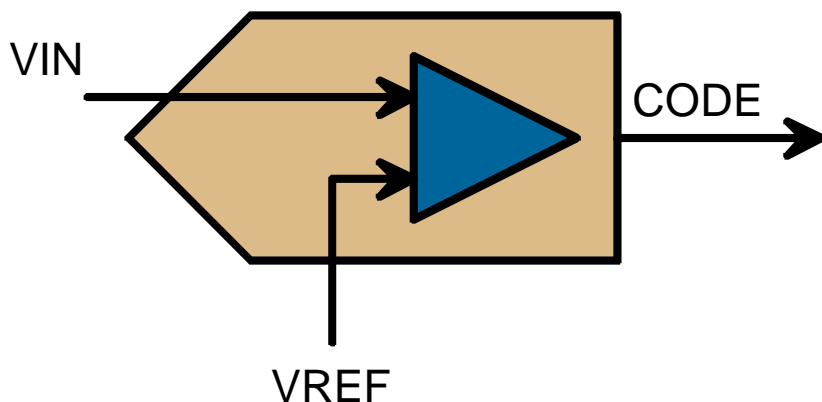
2
$$\left[GBW \geq 4 \cdot f_{ZX} = 4 \cdot 2.5MHz = 10MHz \right.$$

3
$$\left[\begin{aligned} 20 \cdot C_{SH} \leq C_F \leq 60 \cdot C_{SH} &\Rightarrow 20 \cdot 48pF \leq C_F \leq 60 \cdot 48pF \Rightarrow \\ 960pF \leq C_F \leq 2.9nF &\Rightarrow C_F = 1.2nF \end{aligned} \right.$$

4
$$\left[R_F = \frac{1}{2\pi \cdot C_F \cdot f_{ZX}} = \frac{1}{2\pi \cdot 1.2nF \cdot 2.5MHz} = 53\Omega \right.$$

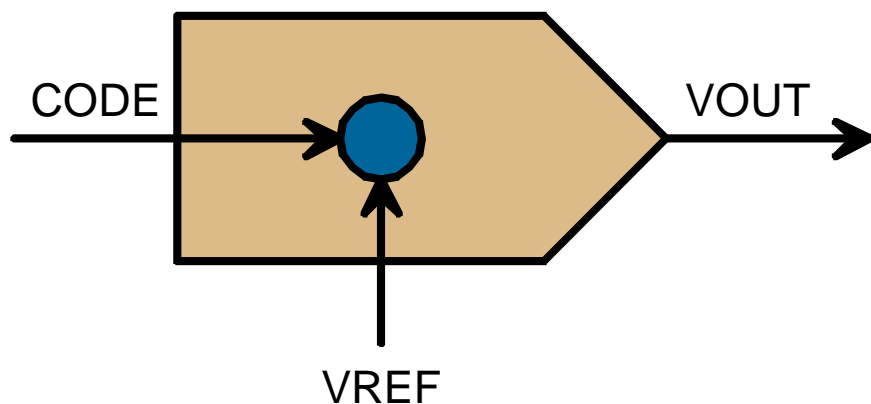


ADC and DAC Functions



ADC :

$$CODE = V_{IN} \cdot \frac{2^N}{V_{REF}}$$



DAC :

$$V_{OUT} = CODE \cdot \frac{V_{REF}}{2^N}$$



Noise and ENOB of ADC

Signal-to-Noise Ratio and Distortion

$$SINAD(dB) = -20 \log \sqrt{10^{\frac{-SNR}{10}} + 10^{\frac{THD}{10}}}$$

Effective Number of Bits

$$ENOB = \frac{SINAD - 1.76dB}{6.02}$$

$$ENOB = f(SNR, THD)$$

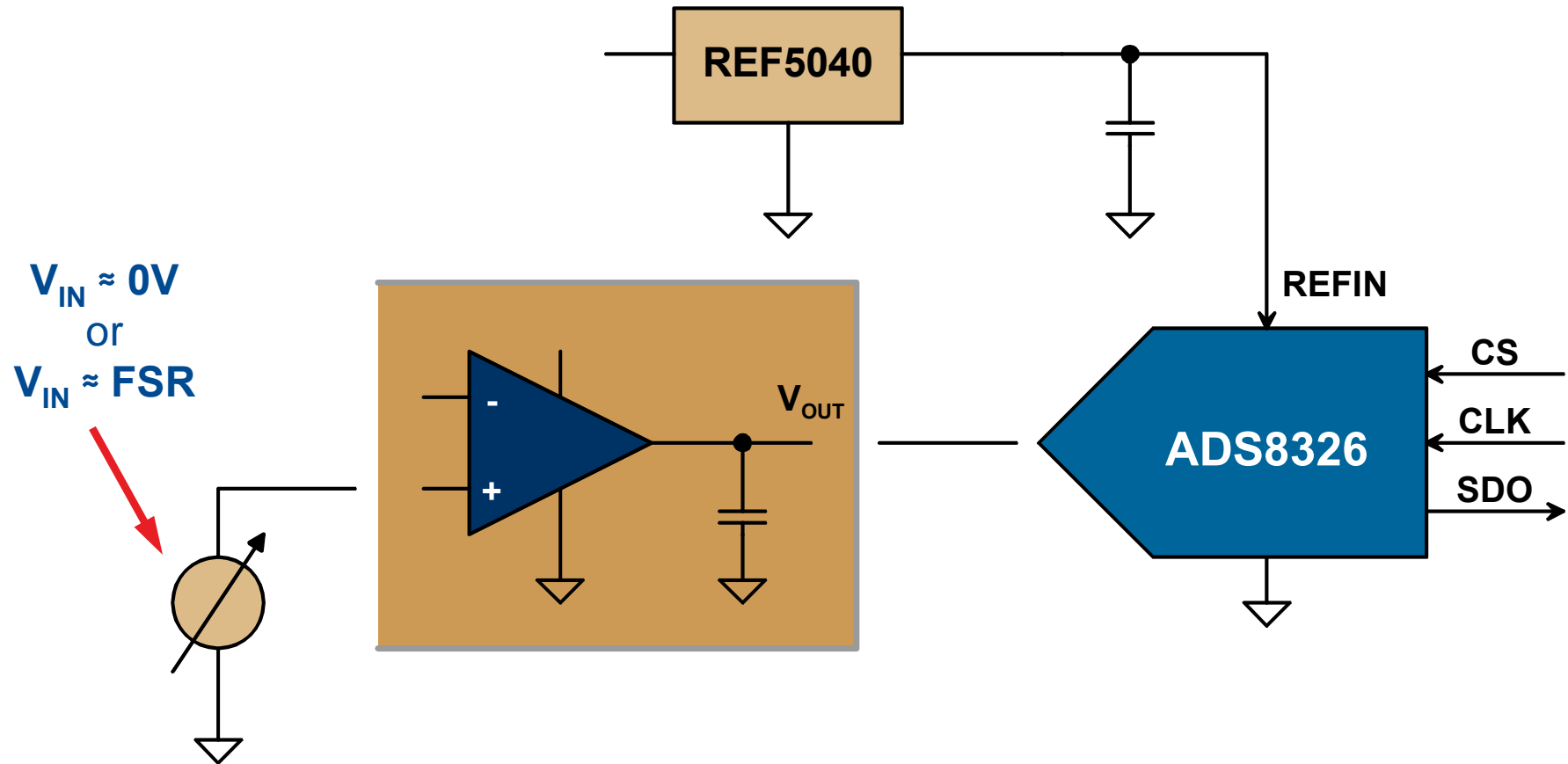


Noise Sources in SAR ADCs

- Wideband ADC internal circuits noise
- Noise due to aperture jitter
- Quantization noise
- Transition or DNL noise
- **Analog input buffer circuit noise**
- **Reference input voltage noise**

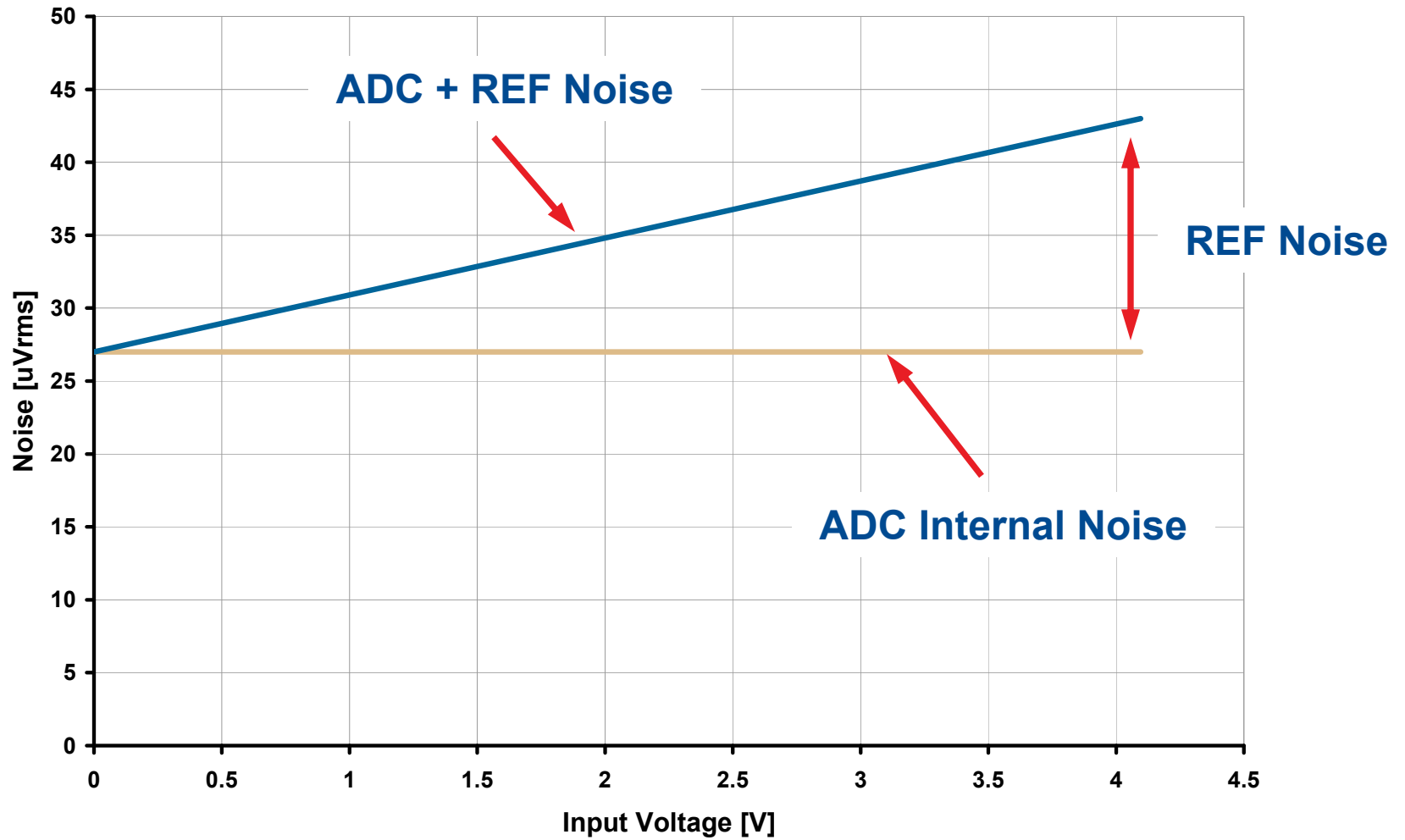


Measuring Reference Input Noise





Noise Contribution



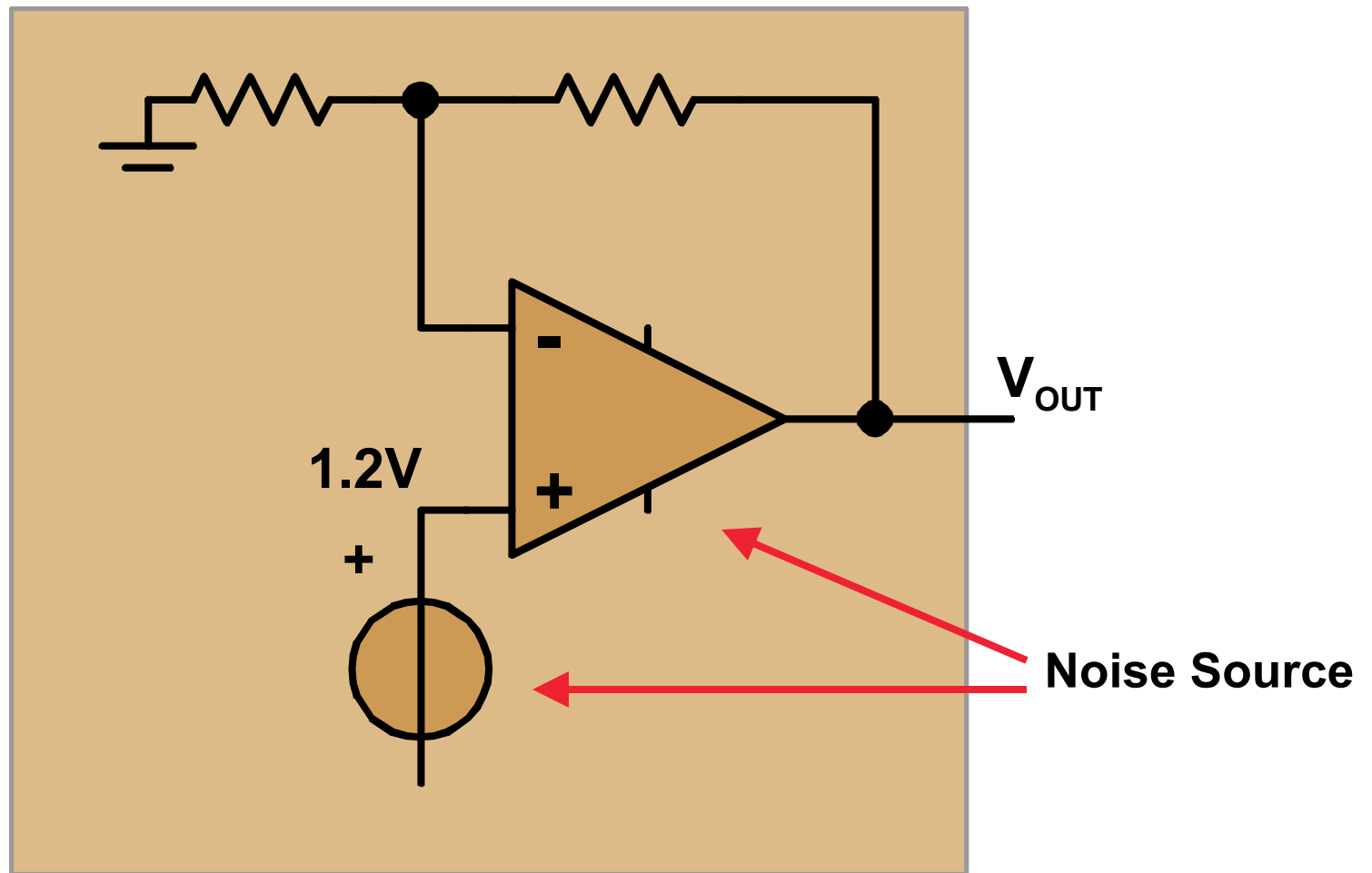


Quantization of Reference Noise

- **Low noise analog input of 0.09V**
 - Source of noise is ADC's internal noise.
 - Measured noise is $27\mu\text{V}_{\text{RMS}}$ or $179\mu\text{V}_{\text{PP}}$
- **Low noise analog input of 4.02V**
 - Source of noise is ADC's internal noise and reference input noise.
 - Measured noise is $43\mu\text{V}_{\text{RMS}}$ or $287\mu\text{V}_{\text{PP}}$

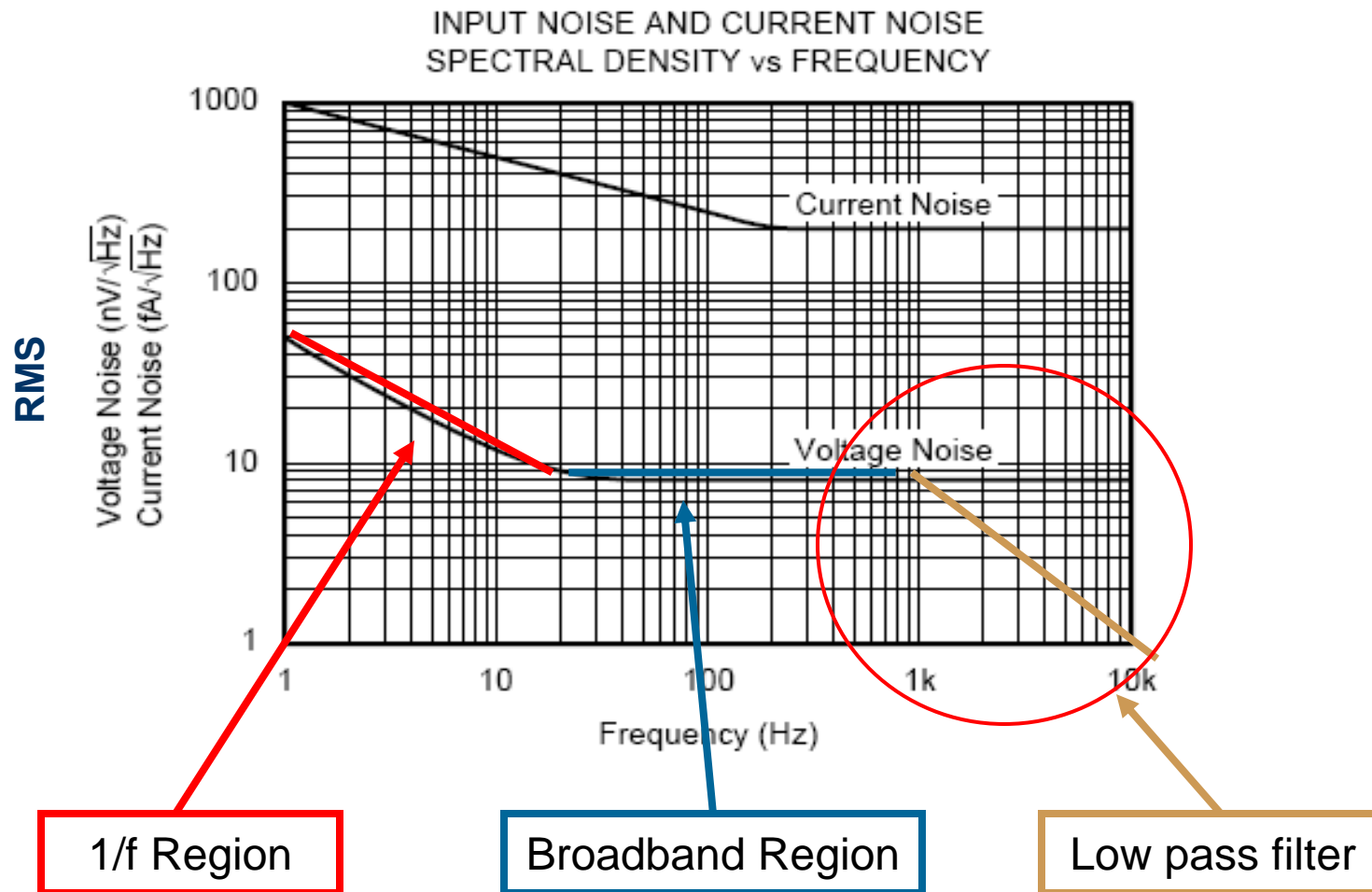


Sources of the Noise in REF50xx





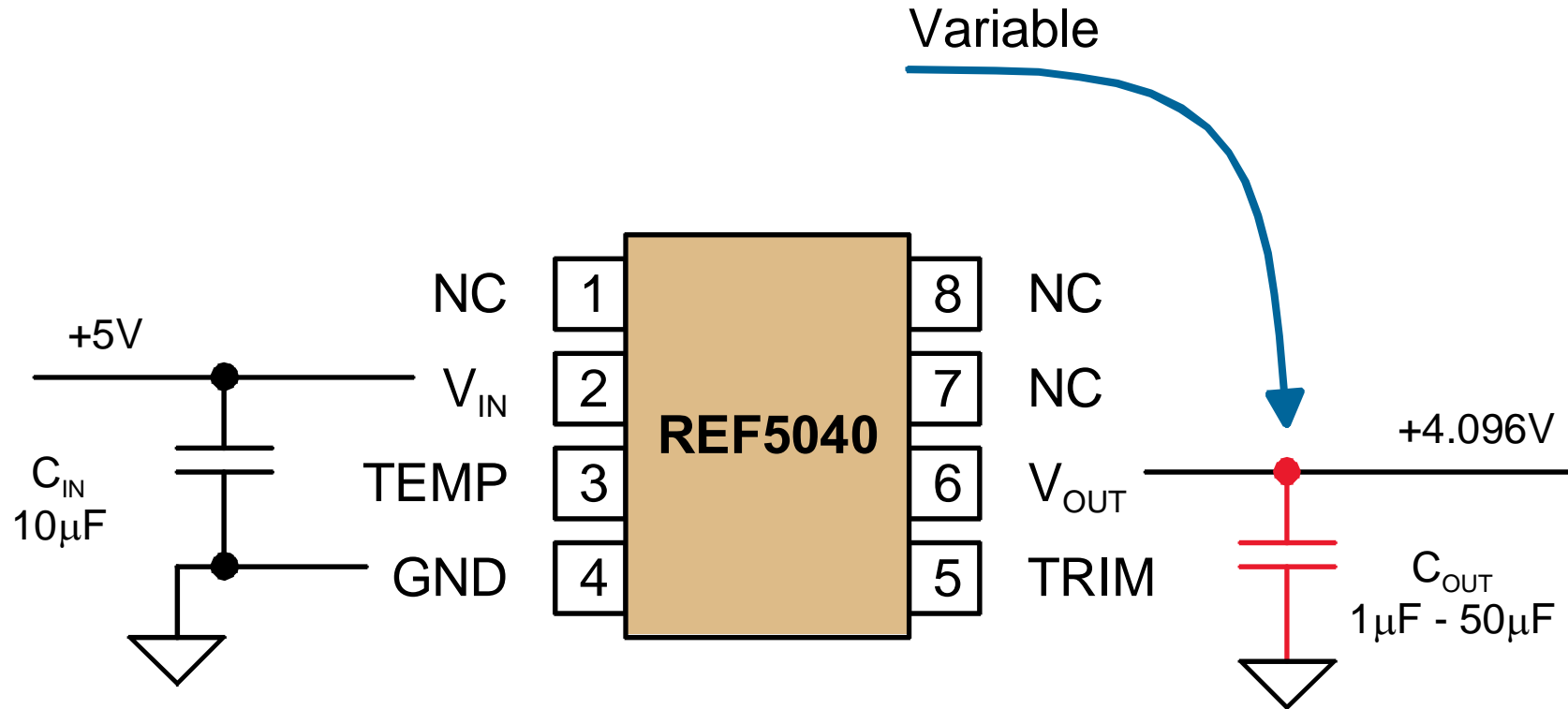
Low Pass Filter Shapes the Output Noise Spectrum



Source: Art Kay; OpAmp Noise 2006

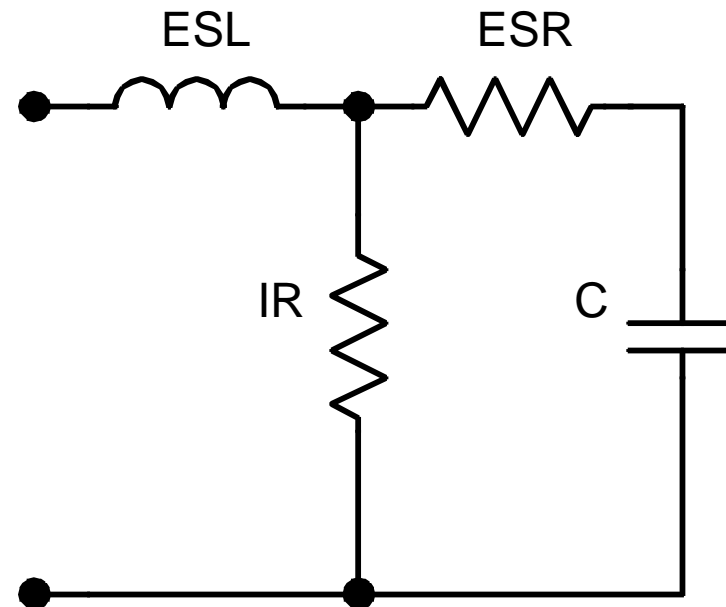


REF50xx Noise Test Circuit





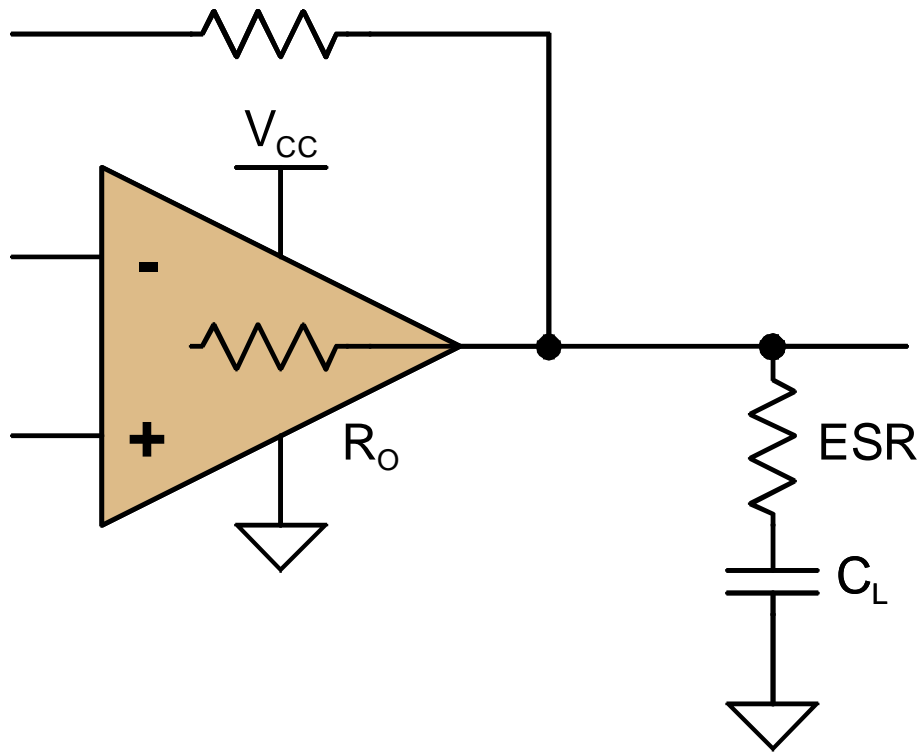
Capacitor Equivalent Circuit



- C Capacitance
- ESR Equivalent Series Resistance
- ESL Equivalent Series Inductance
- IR Insulation Resistance



Capacitive Load with ESR



$$f_P = \frac{1}{2\pi \cdot (R_O + ESR) \cdot C_L}$$

$$f_Z = \frac{1}{2\pi \cdot ESR \cdot C_L}$$



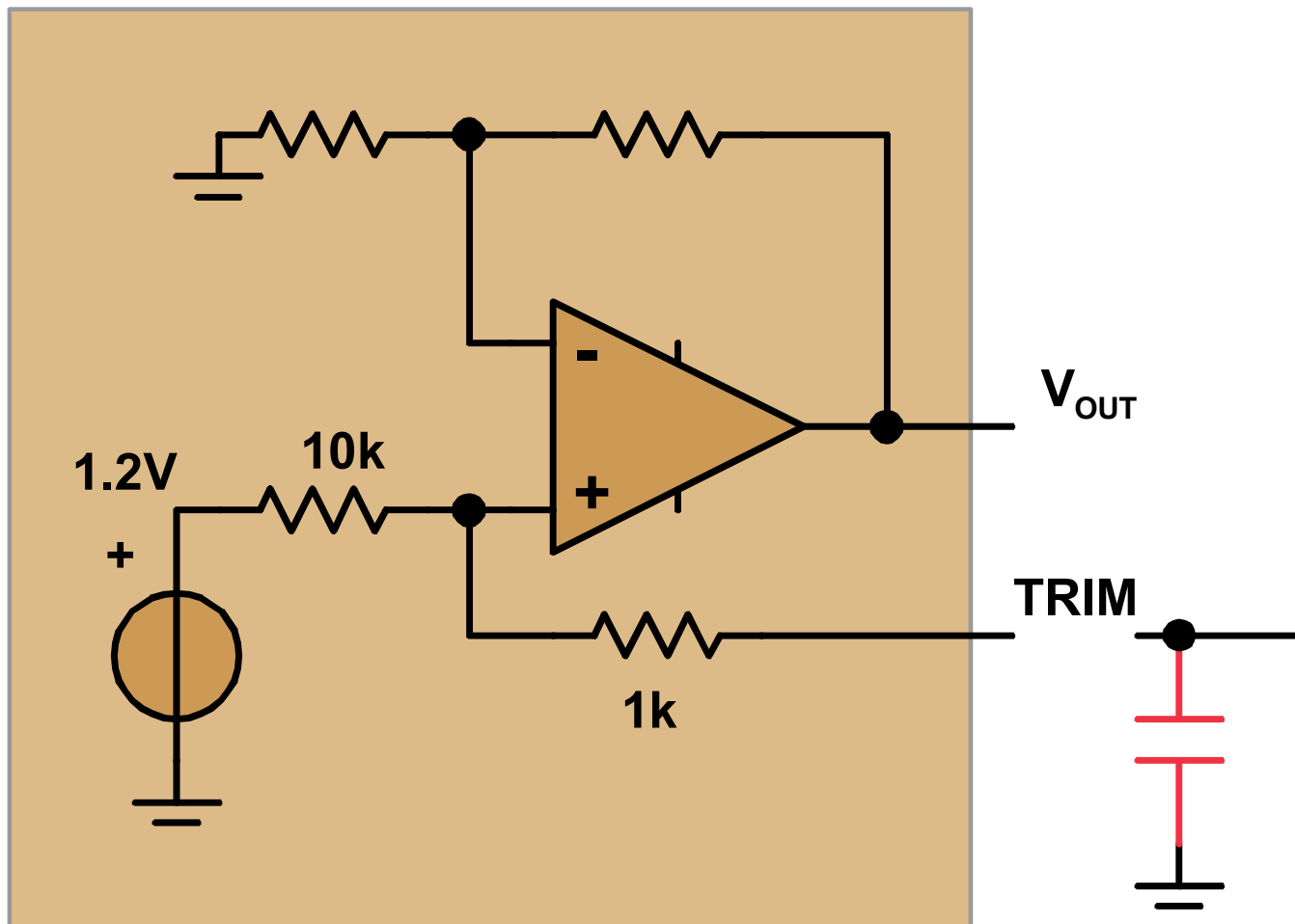
Measured Noise for different BW and LP Filters

Noise	Measurement Bandwidth				Units
	22kHz LP-5P	30kHz LP-3P	80kHz LP-3P	>500kHz	
GND	0.8	1	1.8	4.9	μV_{RMS}
1 μF	37.8	41.7	53.7	9,017	μV_{RMS}
2.2 μF (cer)	<u>41.7</u>	<u>46.2</u>	<u>55.1</u>	<u>60.8</u>	μV_{RMS}
10 μF	33.4	33.4	35.2	38.5	μV_{RMS}
10 μF (cer)	37.1	37.2	37.8	39.1	μV_{RMS}
20 μF (cer)	33.1	33.1	33.2	34.5	μV_{RMS}
47 μF	23.2	23.8	24.1	26.5	μV_{RMS}

The capacitor on the output of REF50xx together with internal components will create Low Pass filters.



Filtering Internal Bandgap Reference





Measured Noise with Added Bandgap Filter

Noise	Measurement Bandwidth				Units
	22kHz LP-5P	30kHz LP-3P	80kHz LP-3P	>500kHz	
GND	0.8	1	1.8	4.6	μV_{RMS}
2.2 μF (cer)	42.5	47.2	61.2	68.3	μV_{RMS}
2.2 μF +1 μF	<u>17.5</u>	<u>19.4</u>	<u>22.6</u>	<u>24.5</u>	μV_{RMS}
10 μF	34.4	35.6	37.7	44.5	μV_{RMS}
10 μF +1 μF	<u>14.1</u>	<u>14.4</u>	<u>14.9</u>	<u>16.4</u>	μV_{RMS}
20 μF (cer)	34.8	34.9	35.1	35.2	μV_{RMS}
20 μF +1 μF	<u>14.4</u>	<u>14.4</u>	<u>14.7</u>	<u>15.1</u>	μV_{RMS}

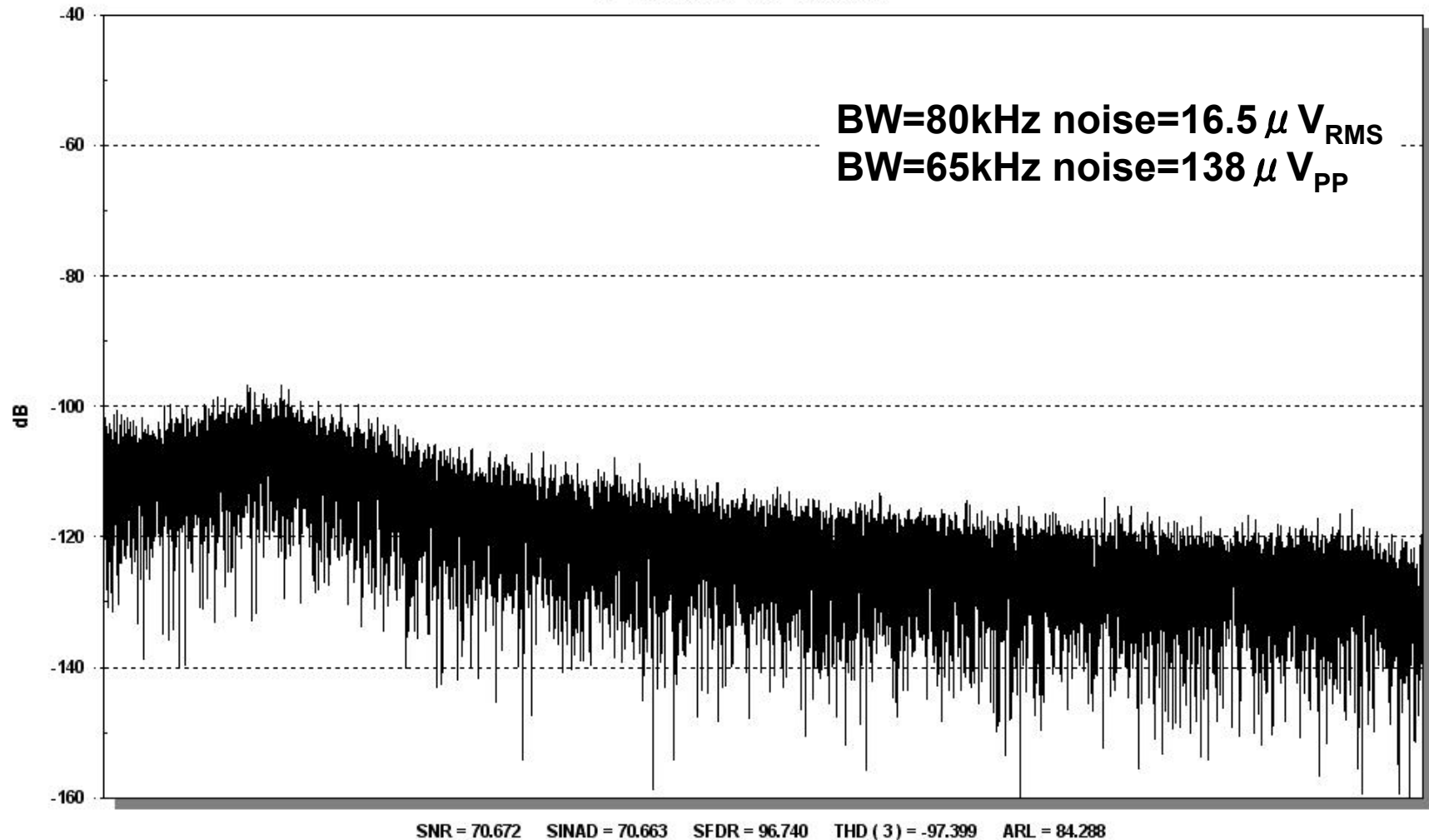
Adding 1 μF capacitor on the TRIM pin will reduce noise **~2.5x**



REF5040 Output with $10\ \mu\text{F}$ and $<10\text{m}\ \Omega$ ESR Capacitor

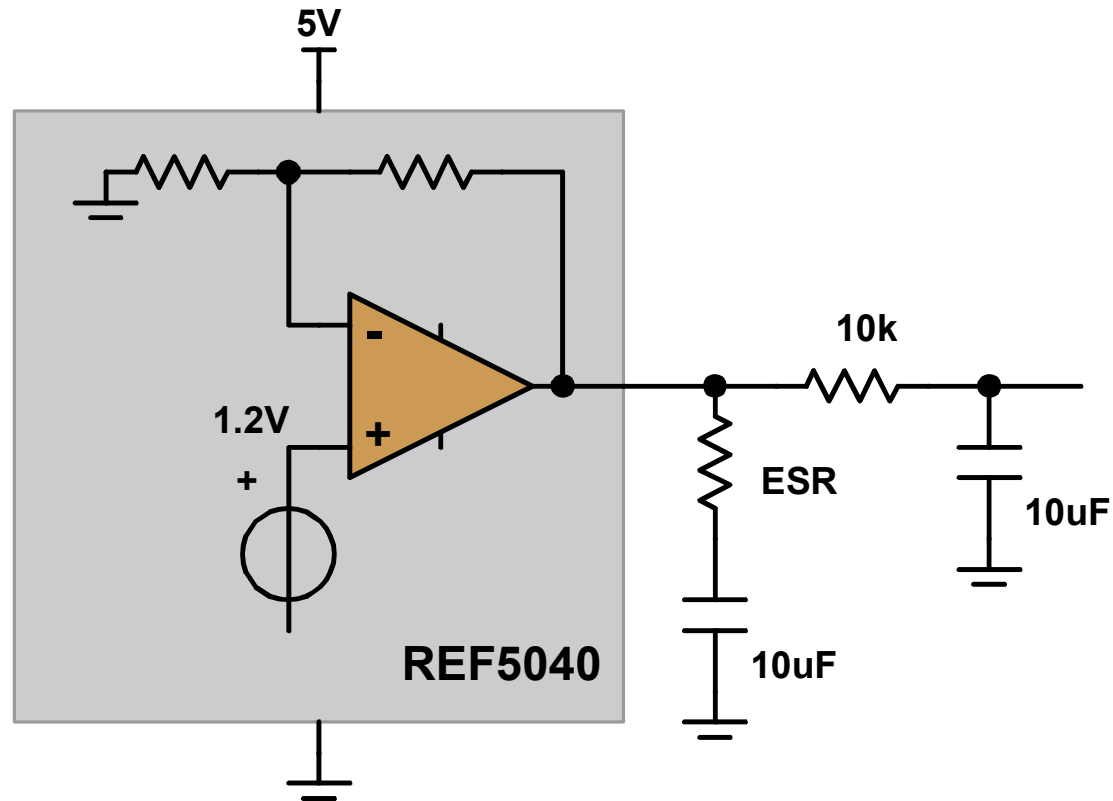
Frequency Spectrum (32768 Point FFT)

$F_s = 131.0720\ \text{kHz}$ $F_{in} = 4.000000\ \text{Hz}$





Added RC filter on the Output



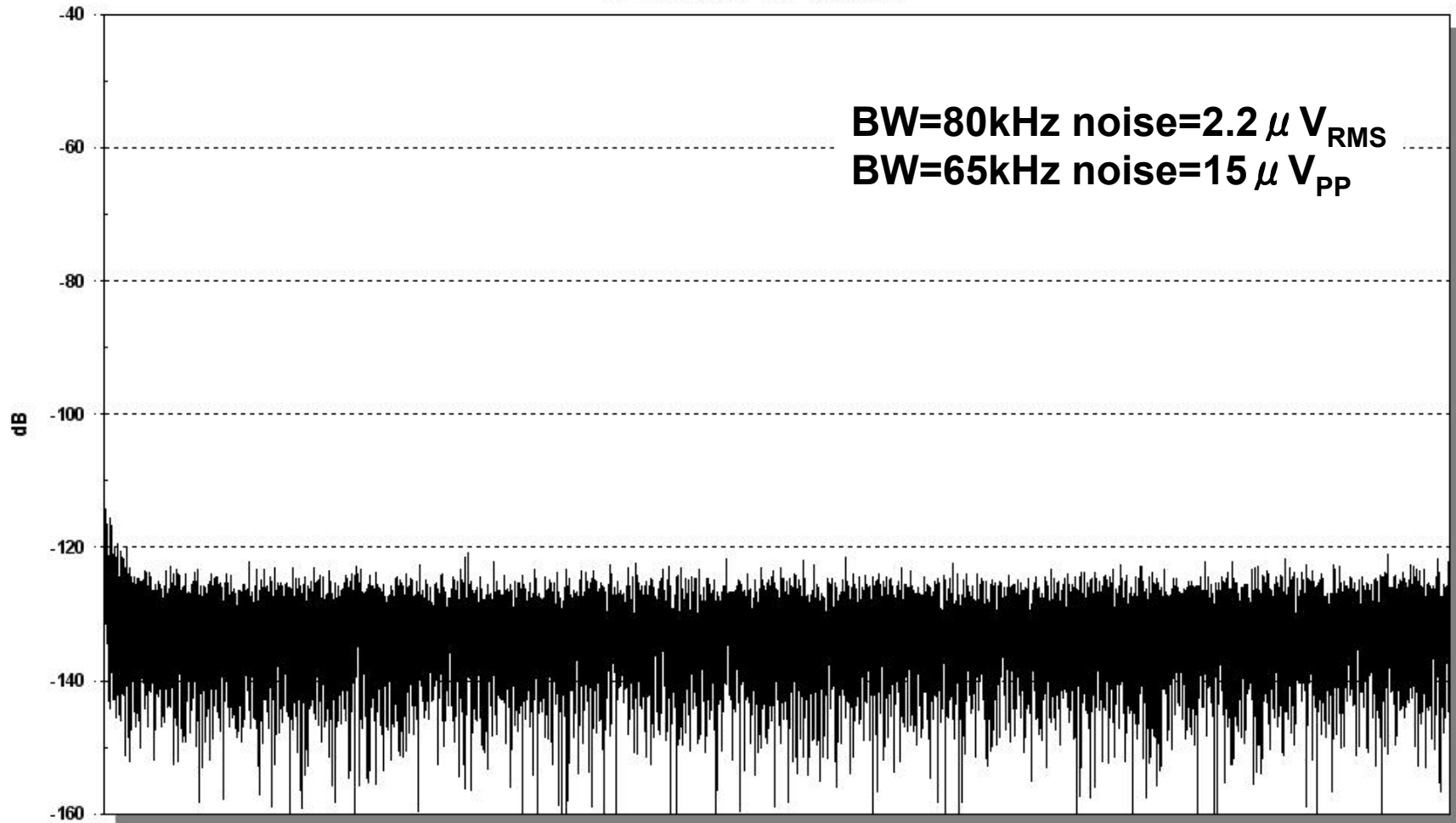
Adding RC filter reduce noise from xx to xx



REF5040 Output with added RC Filter

Frequency Spectrum (32768 Point FFT)

Fs = 131.0720 kHz Fin = 8.000000 Hz

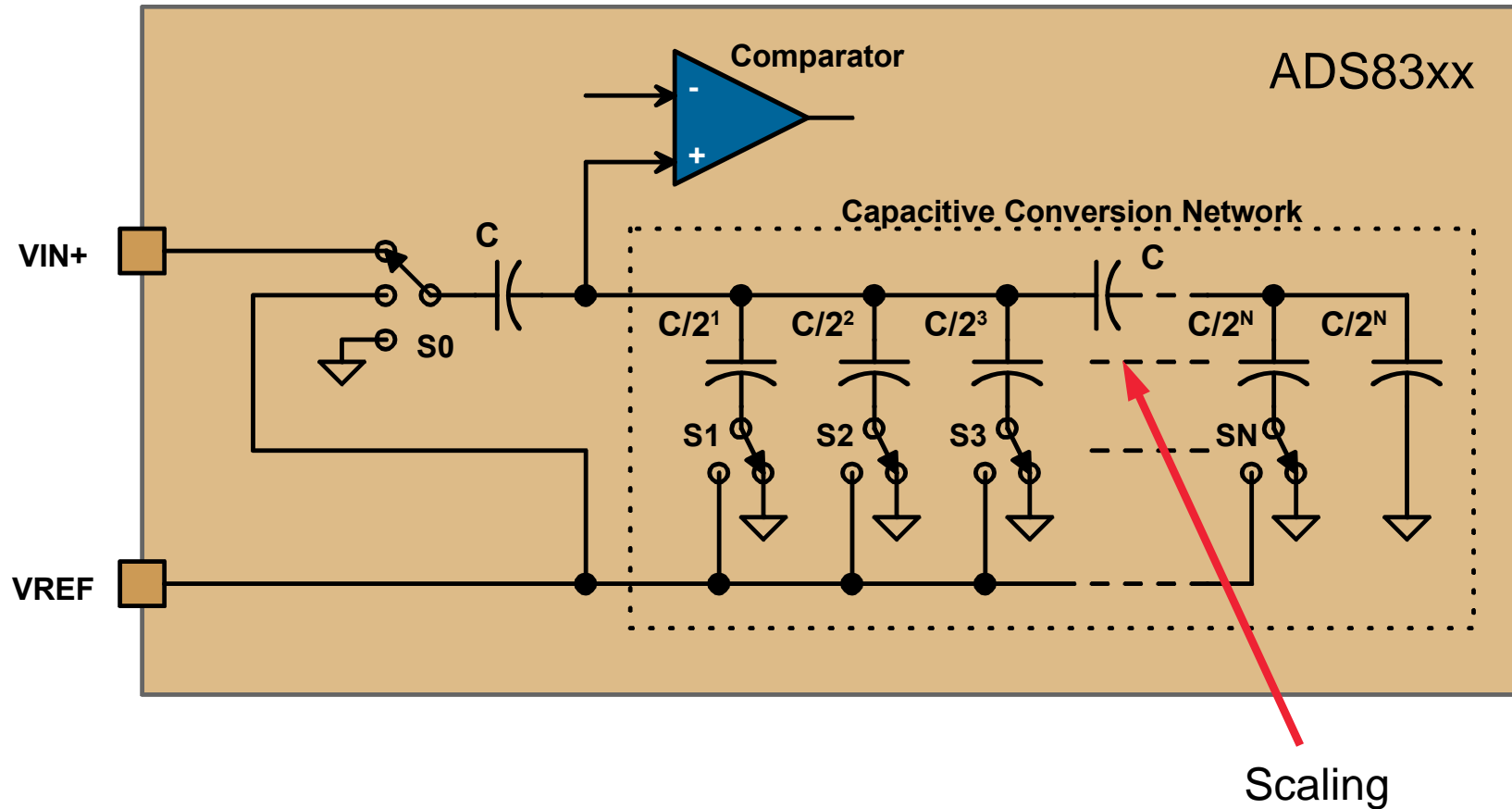


BW=80kHz noise= $2.2 \mu V_{RMS}$
BW=65kHz noise= $15 \mu V_{PP}$

SNR = 88.594 SINAD = 88.571 SFDR = 110.237 THD (3) = -111.373 ARL = 84.288

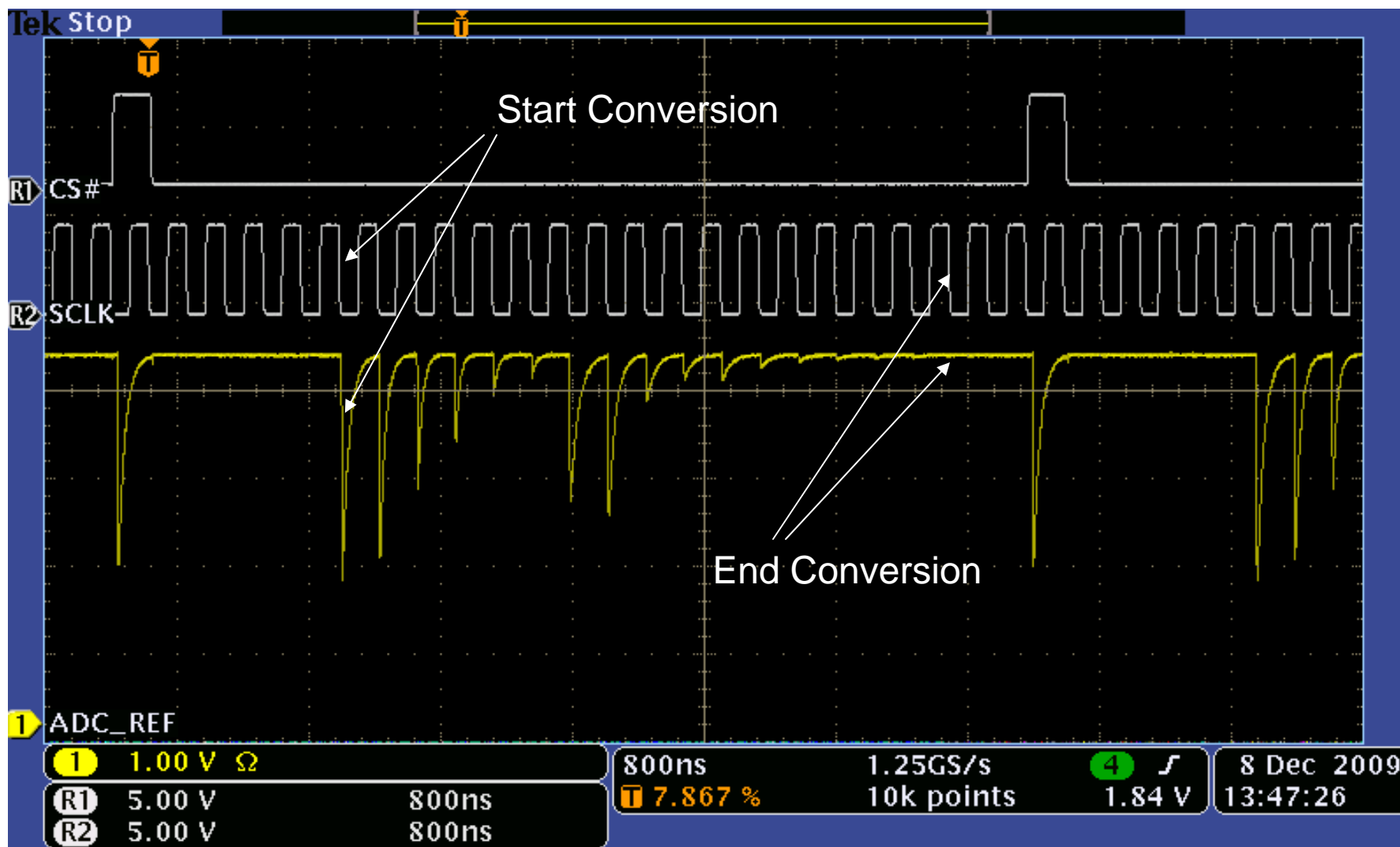


SAR ADC Capacitive Conversion Network



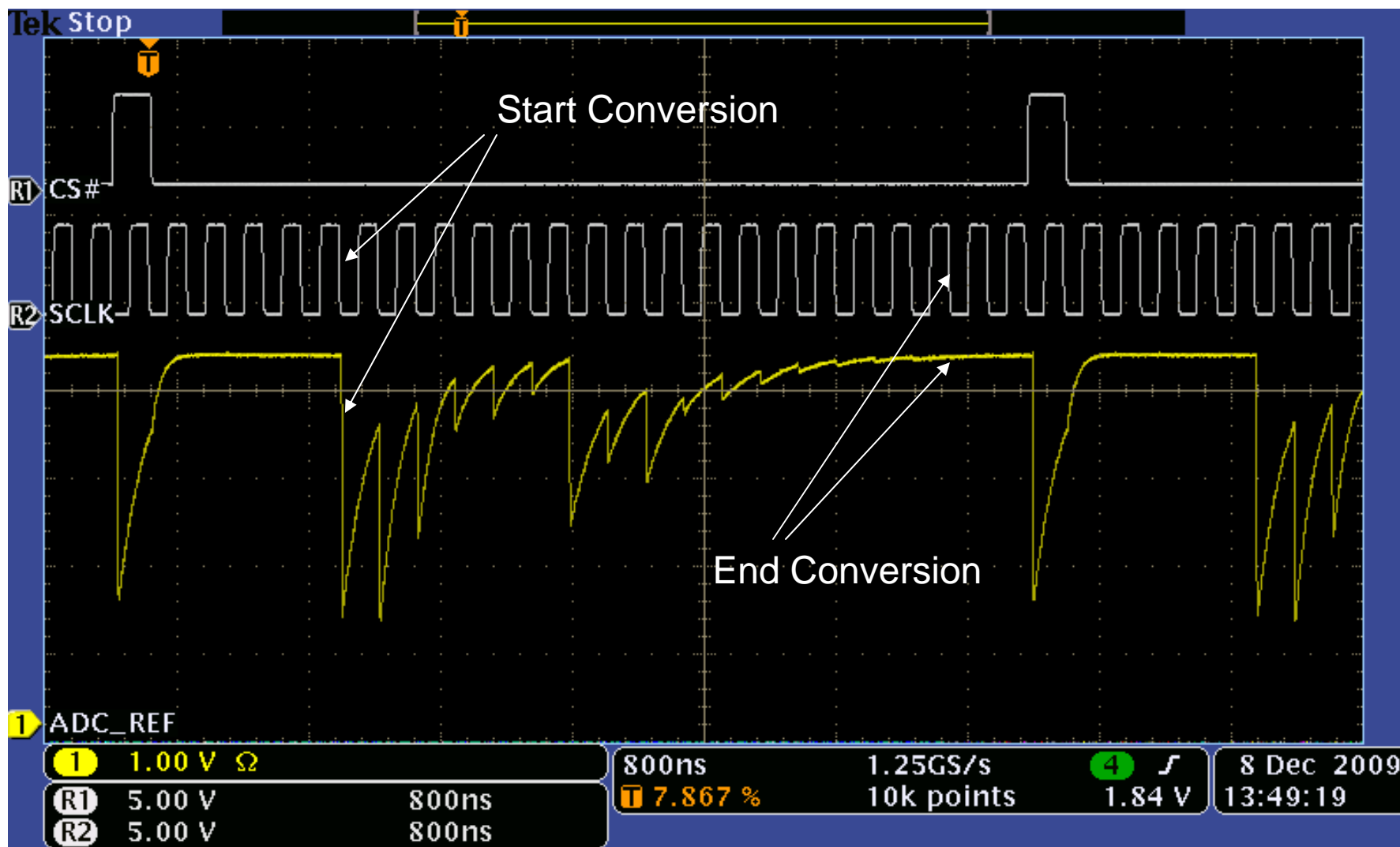


REF Input With Proper Buffer



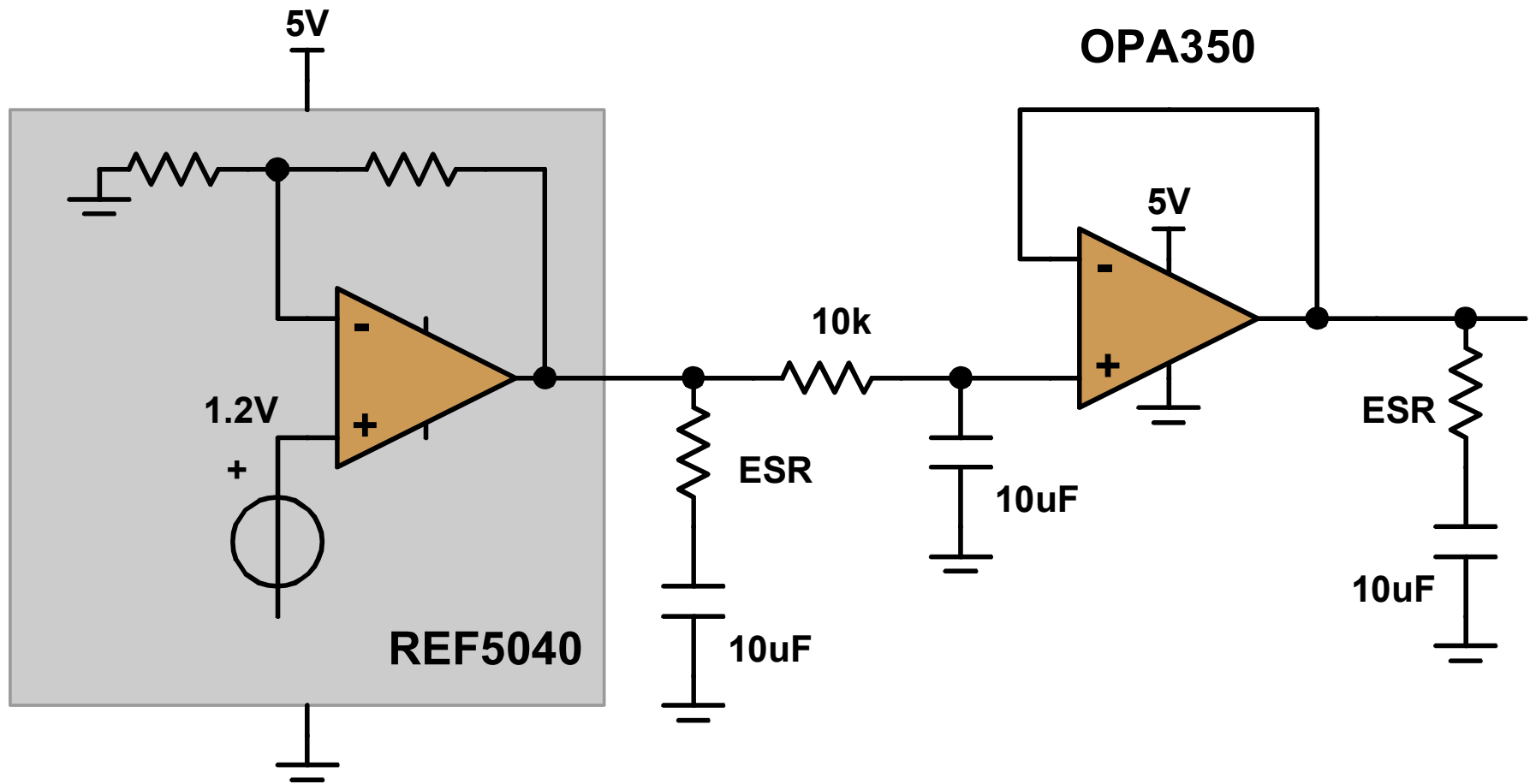


REF Input With Wrong Buffer





Voltage-reference circuit with added buffer and output filter



$BW=80\text{kHz}$ noise= $4.5 \mu\text{V}_{\text{RMS}}$
 $BW=65\text{kHz}$ noise= $42 \mu\text{V}_{\text{PP}}$



Design by Example

1. Use REF5040 and $10 \mu\text{F}$ with $0.5 \Omega < \text{ESR} < 1.5 \Omega$ ($V_n = 39 \mu\text{V}_{\text{RMS}} / 261 \mu\text{V}_{\text{PP}}$)
2. Add $1 \mu\text{F}$ on the TRIM pin ($V_n = 16 \mu\text{V}_{\text{RMS}} / 138 \mu\text{V}_{\text{PP}}$)
3. Use additional RC Filter ($10\text{k}\Omega / 10 \mu\text{F}$) ($V_n = 2.2 \mu\text{V}_{\text{RMS}} / 15 \mu\text{V}_{\text{PP}}$)
4. Buffer output with OPA350 and $10 \mu\text{F}$ with $0.2 \Omega < \text{ESR}$ ($V_n = 4.5 \mu\text{V}_{\text{RMS}} / 42 \mu\text{V}_{\text{PP}}$)



References

- 1) Green, Tim, “Operational Amplifier Stability, Part 6 of 15: Capacitance-Load Stability: RISO, High Gain & CF, Noise Gain,” Analog Zone, 2005.
- 2) Miro Oljaca, and Baker Bonnie, “Start with the right op amp when driving SAR ADCs,” EDN, October 16, 2008,
- 3) Downs, Rick, and Miro Oljaca, “Designing SAR ADC Drive Circuitry, Part I: A Detailed Look at SAR ADC Operation,” Analog Zone, 2005.
- 4) Downs, Rick, and Miro Oljaca, “Designing SAR ADC Drive Circuitry, Part II: Input Behavior of SAR ADCs,” Analog Zone, 2005.
- 5) Downs, Rick, and Miro Oljaca, “Designing SAR ADC Drive Circuitry, Part III: Designing The Optimal Input Drive Circuit For SAR ADCs,” Analog Zone, 2007.
- 6) Baker, Bonnie, and Miro Oljaca, “External components improve SAR-ADC accuracy,” EDN, June 7, 2007,
- 7) Miroslav Oljaca, “Understand the Limits of Your ADC Input Circuit Before Starting Conversions,” Analog Zone, 2004.



References Cont.

- 8) **Art Kay, “Analysis and Measurement of Intrinsic Noise in Op Amp Circuits Part 1 to 8”, Analog Zone / En-Genius, 2006-2008**
- 9) **Oljaca, M., Klein, W., “Converter voltage reference performance improvement secrets”, Instrumentation & Measurement Magazine, IEEE, Volume: 12 Issue: 5 October 2009, Page(s): 21-27,**
- 10) **Bonnie Baker, and Miro Oljaca, "How the voltage reference affects ADC performance, Part 3 of 3", Analog Applications Journal, Texas Instruments, Q4Y09, 2009**
- 11) **Miro Oljaca, and Bonnie Baker, "How the Voltage Reference Affects your Performance: Part 2 of 3", Analog Applications Journal, Texas Instruments, Q3Y09, July 2009**
- 12) **Bonnie Baker, and Miro Oljaca, “How the Voltage-reference affects Your Performance: Part 1 of 3”,, Analog Applications Journal, Texas Instruments, Q2Y09, 2009**
- 13) **Miro Oljaca, “Converter Voltage Reference Performance Improvement Secrets” Embedded Systems Conference, Silicon Valley, 2008**



Questions?

Thanks for Your Interest
in
From Analog to Digital:
Design In a Few Simple Steps

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